

FIG. 1

FIG. 1 is a cross-sectional view of a semiconductor device 100. The device includes a substrate 102, a thin layer 104, and a layer 106. A central region 120 is defined by a top layer 110 and side walls 112 and 114. The width of region 120 is labeled W. The height of the side walls 112 and 114 is labeled h. A layer 116 is formed on top of 108 within the central region 120. A layer 190 is formed on top of 108 outside the central region 120.

FIG. 2

The diagram illustrates a semiconductor device 100 in cross-section. It features a substrate 116 with a central layer 118. On top of layer 118 are two gate electrodes 120 and 122. A dashed line 101 indicates a horizontal path through the device. A temperature sensor 240 is connected to the device. A voltage source \$V_G\$ is connected to the gates. A meter 204 is connected to the device via terminal 205. The device is controlled by a controller 230 containing CPU, I/O, memory, and circuit components.

2/55

FIG. 4

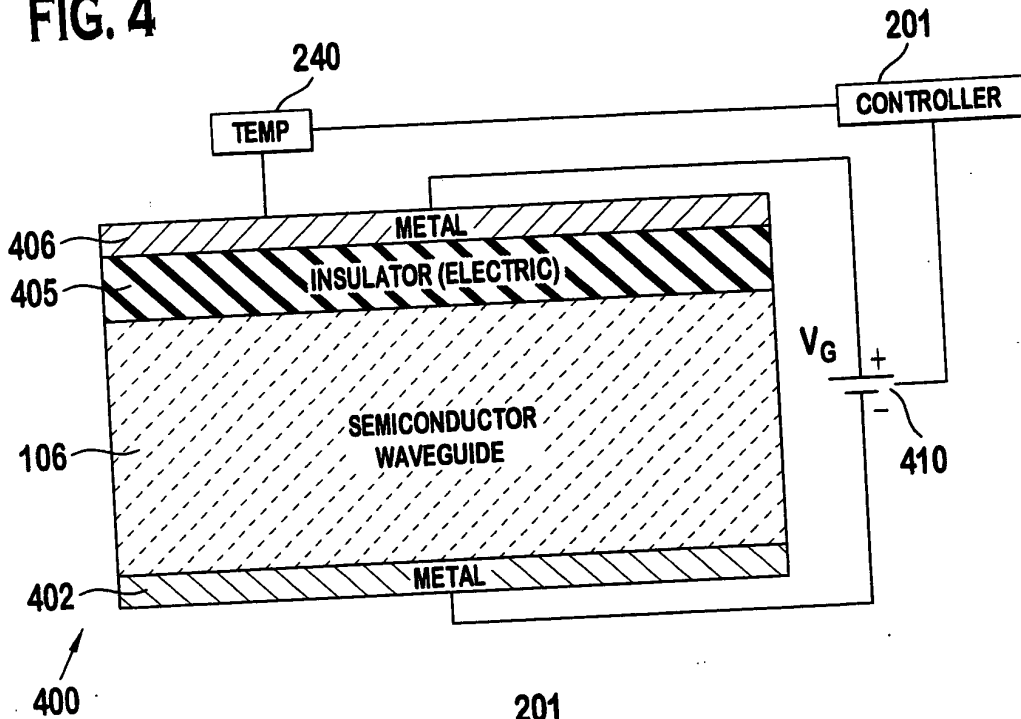
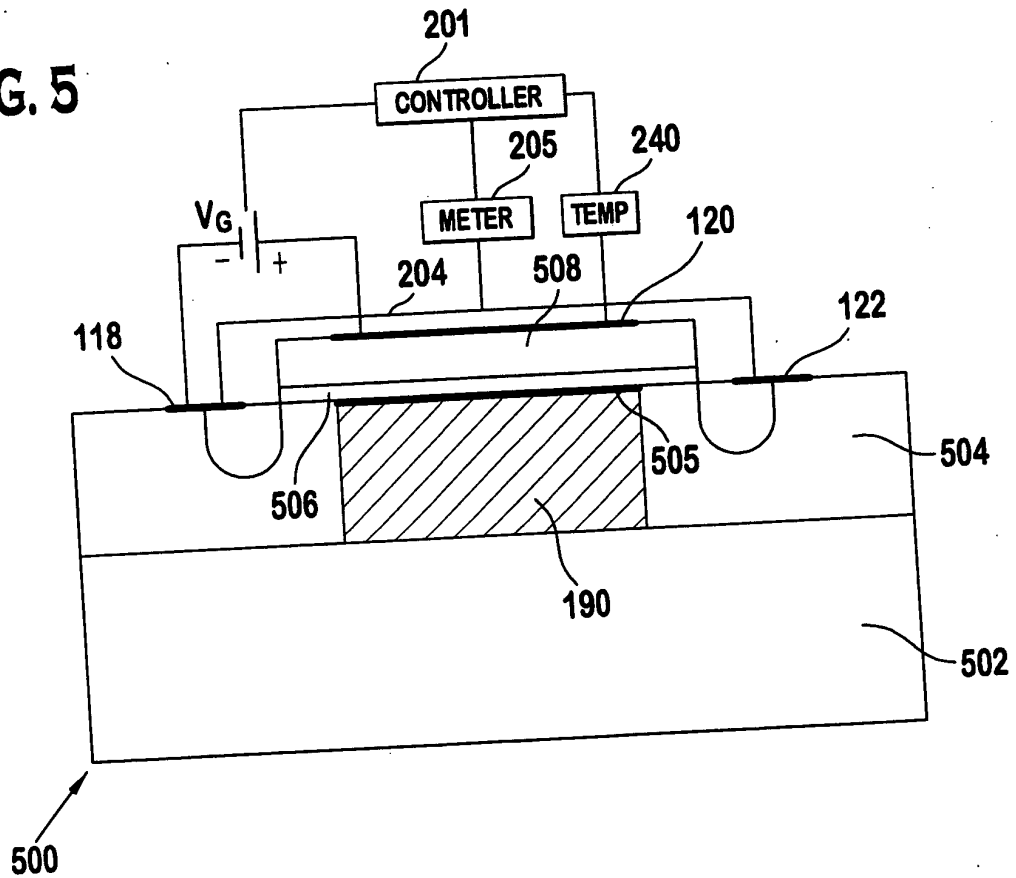


FIG. 5



2002ED-8996700F

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FIG. 6

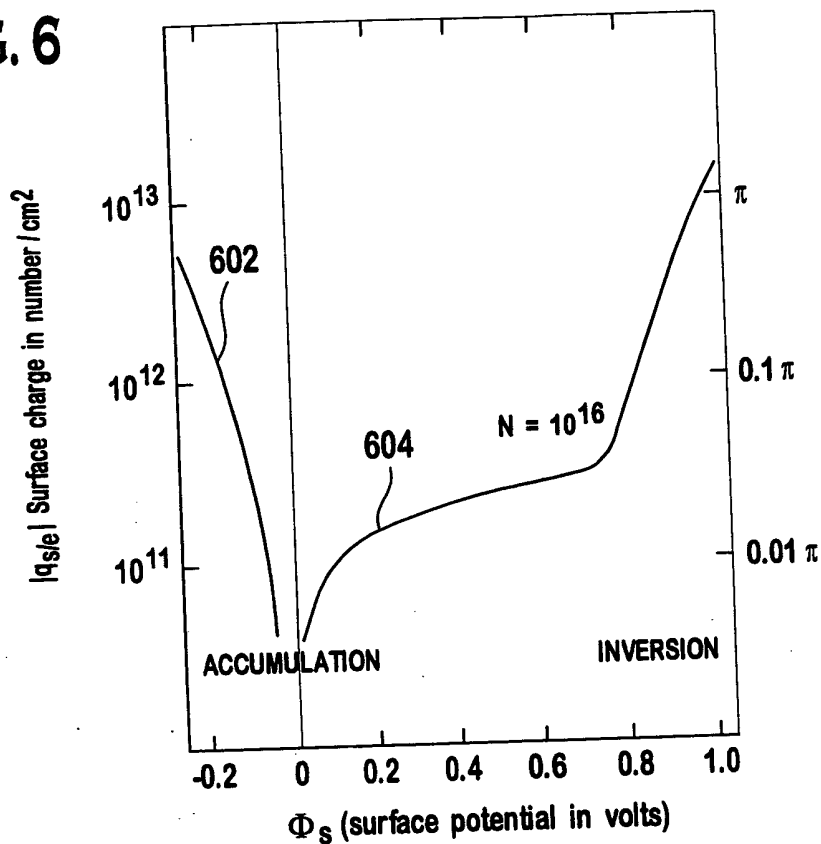
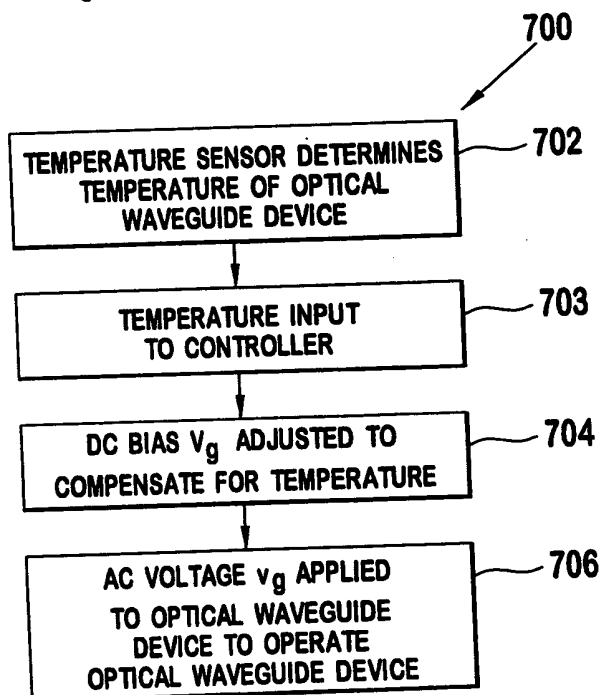


FIG. 7



4/55

FIG. 8

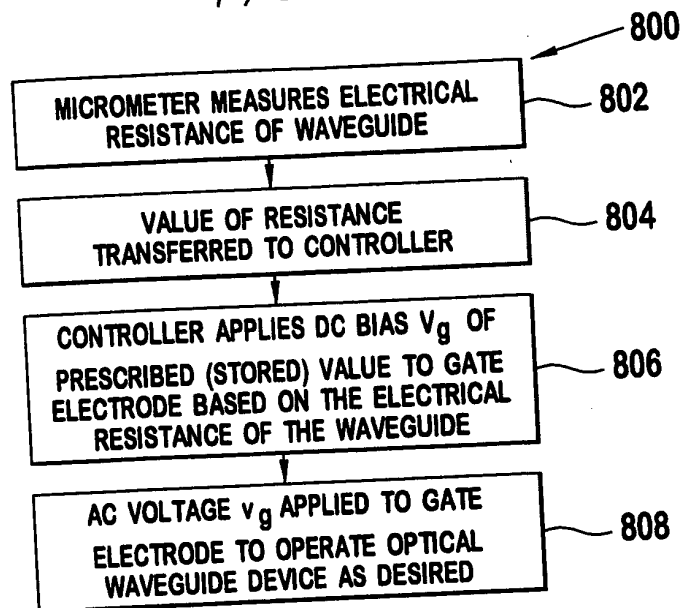


FIG. 9

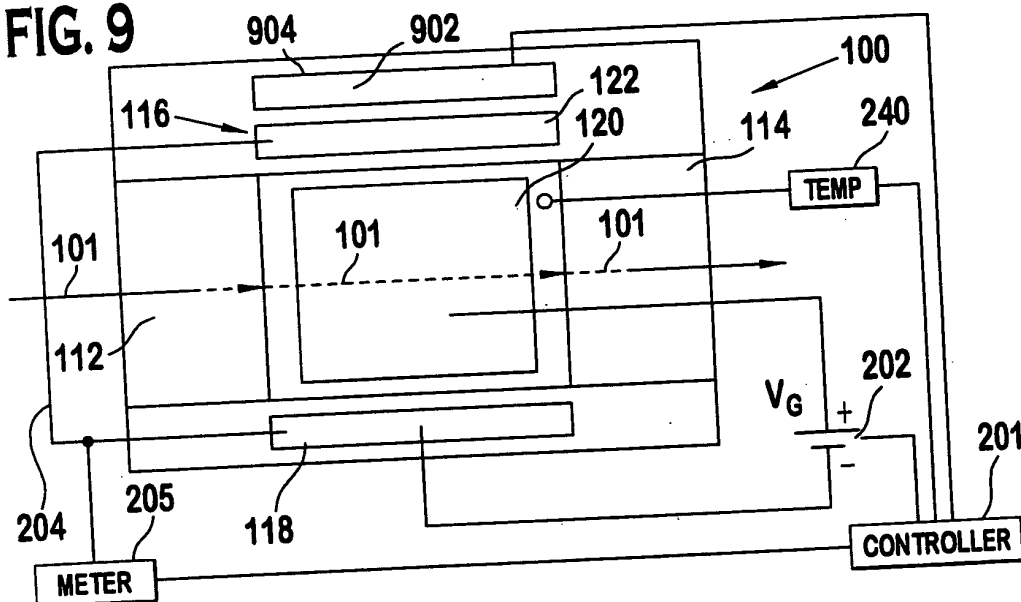
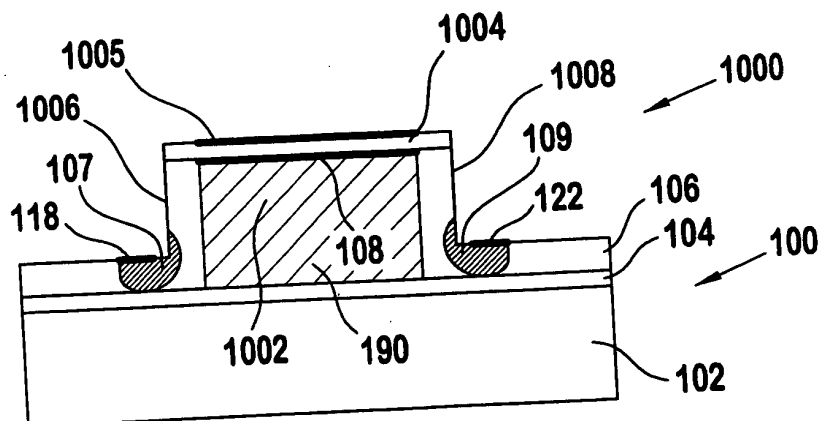


FIG. 10



5/55

FIG. 11

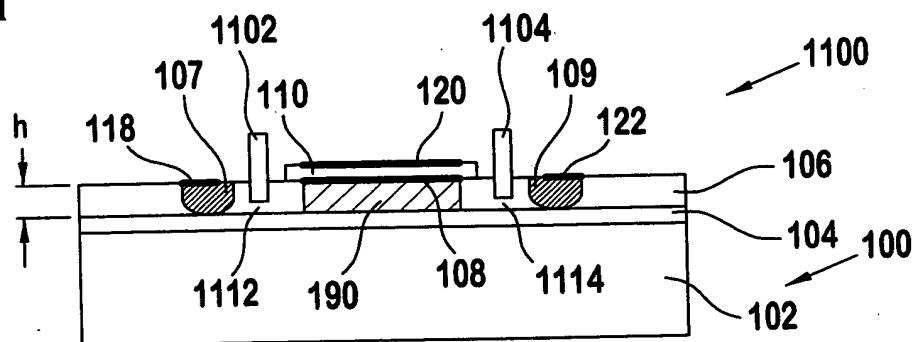


FIG. 12

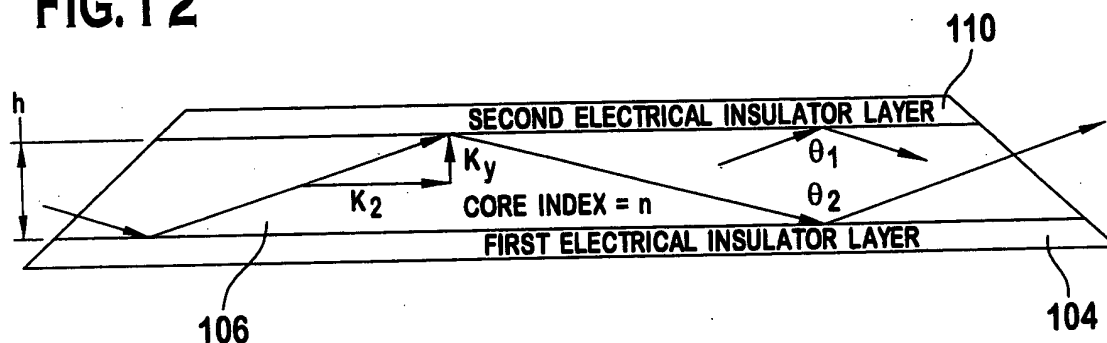


FIG. 13

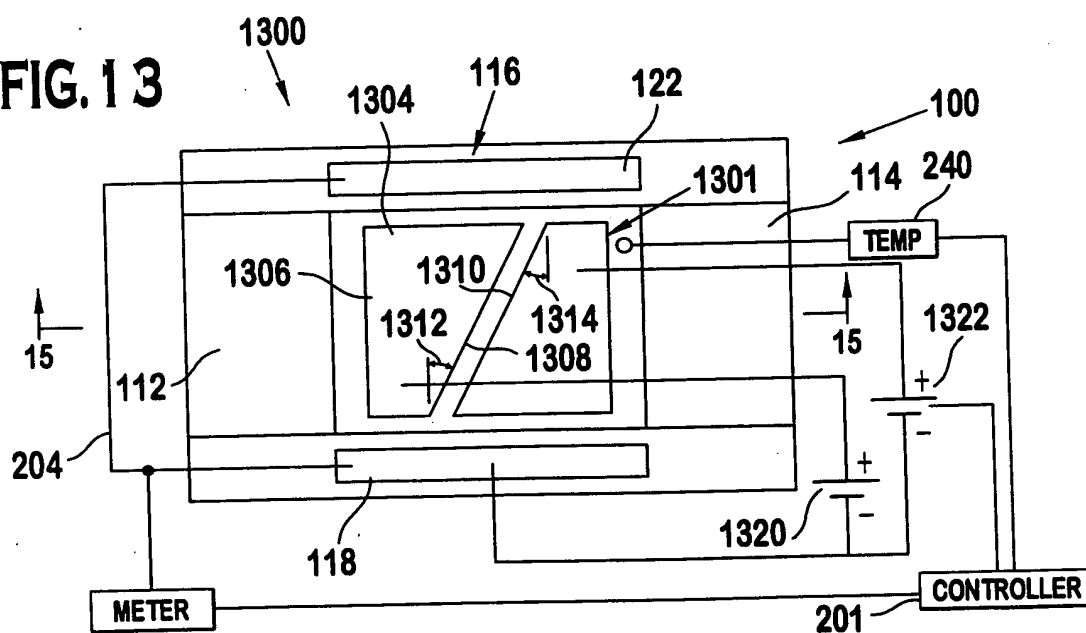
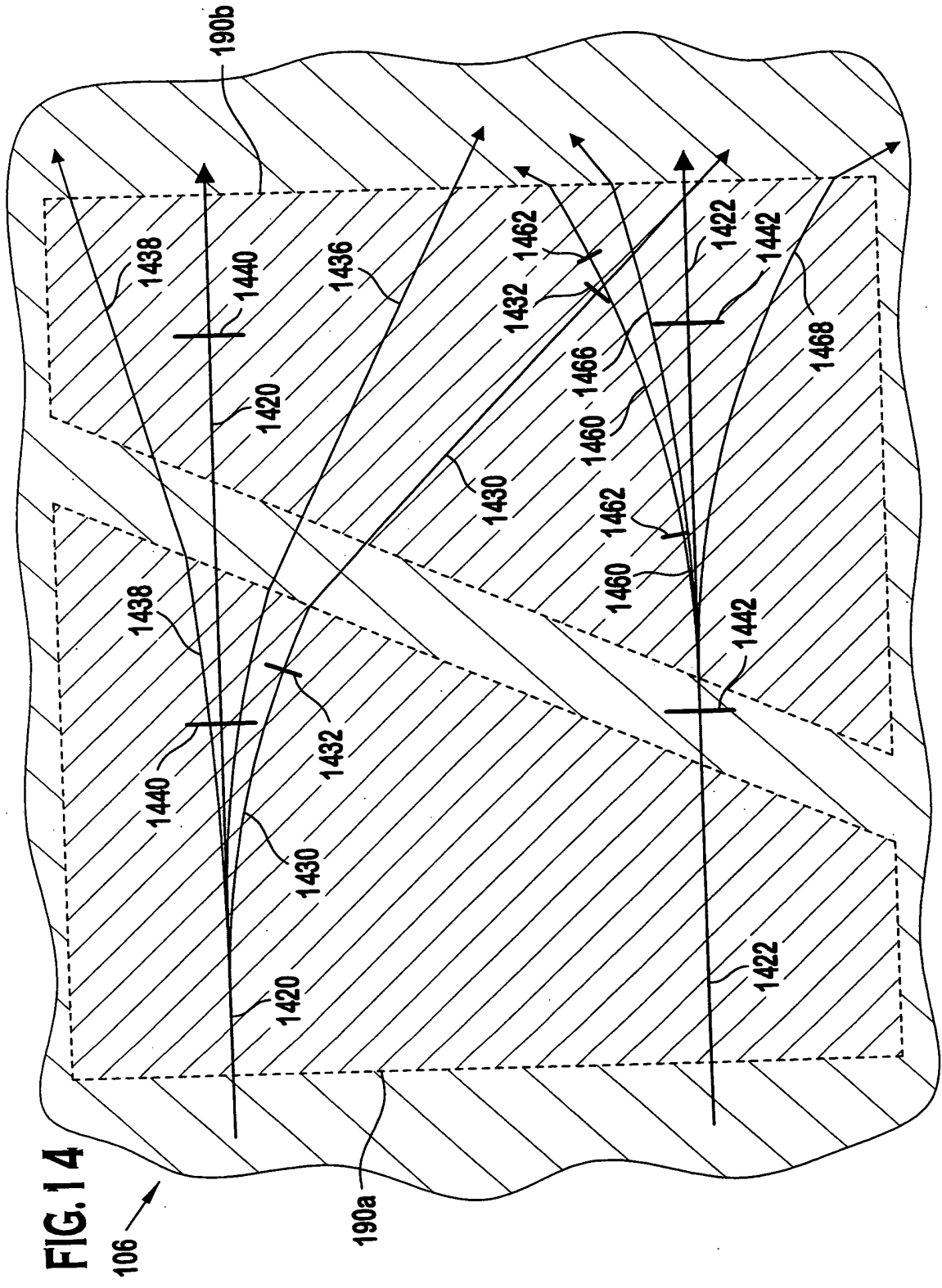


FIG. 14



7/55

FIG. 15A

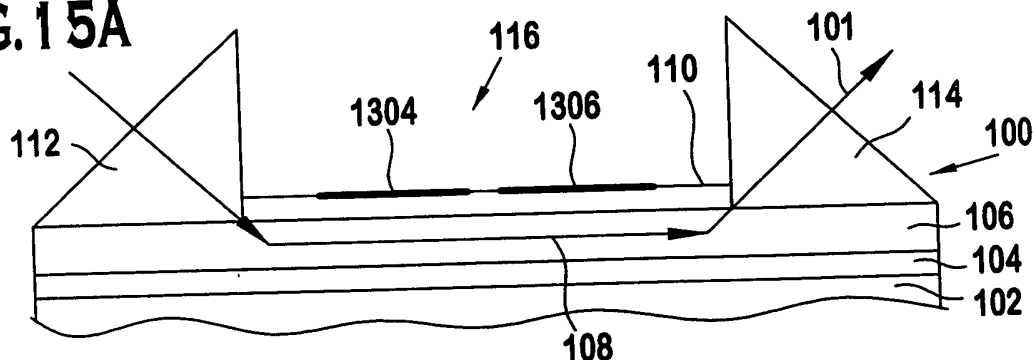


FIG. 15B

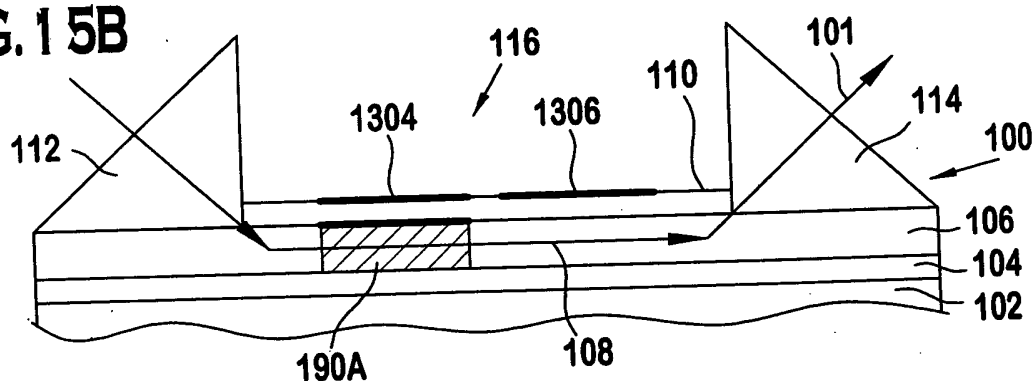


FIG. 15C

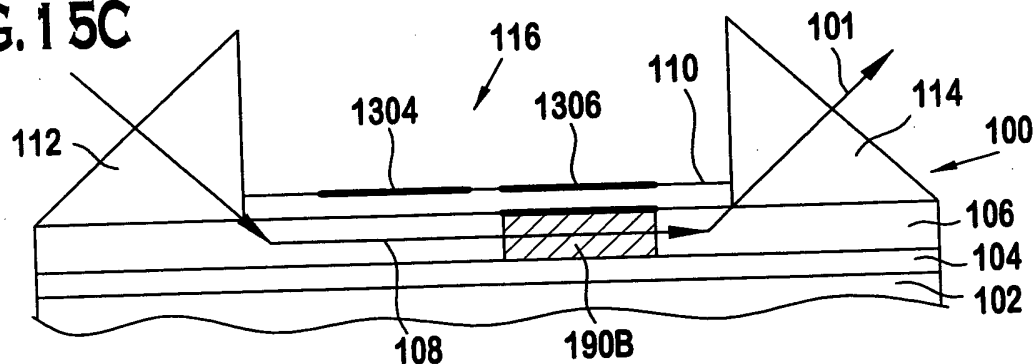
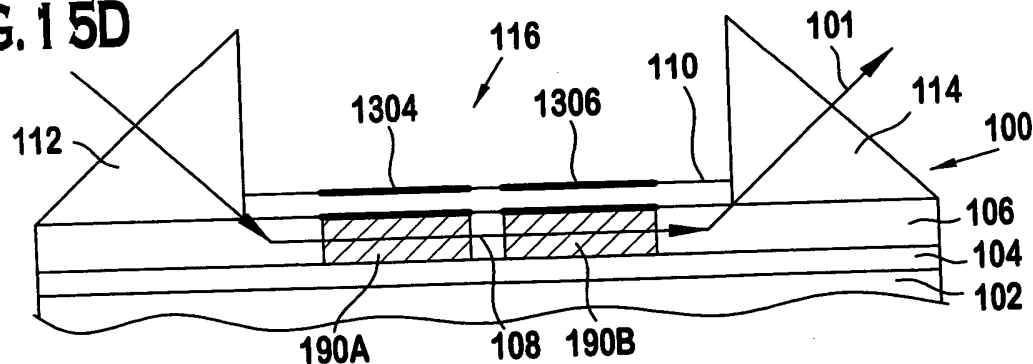


FIG. 15D



200220-8996/00T

8/55

FIG. 16

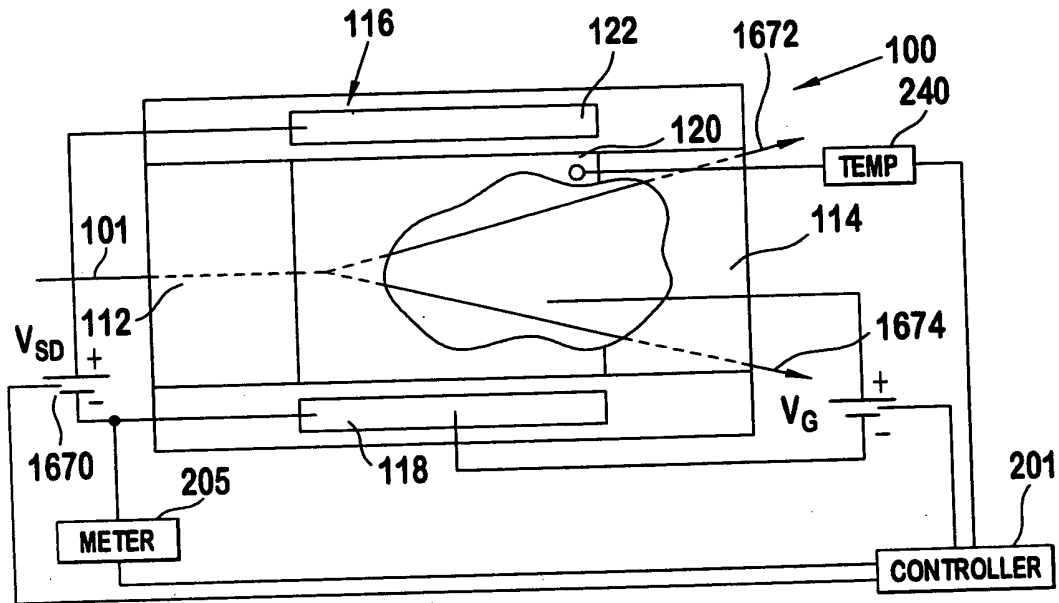
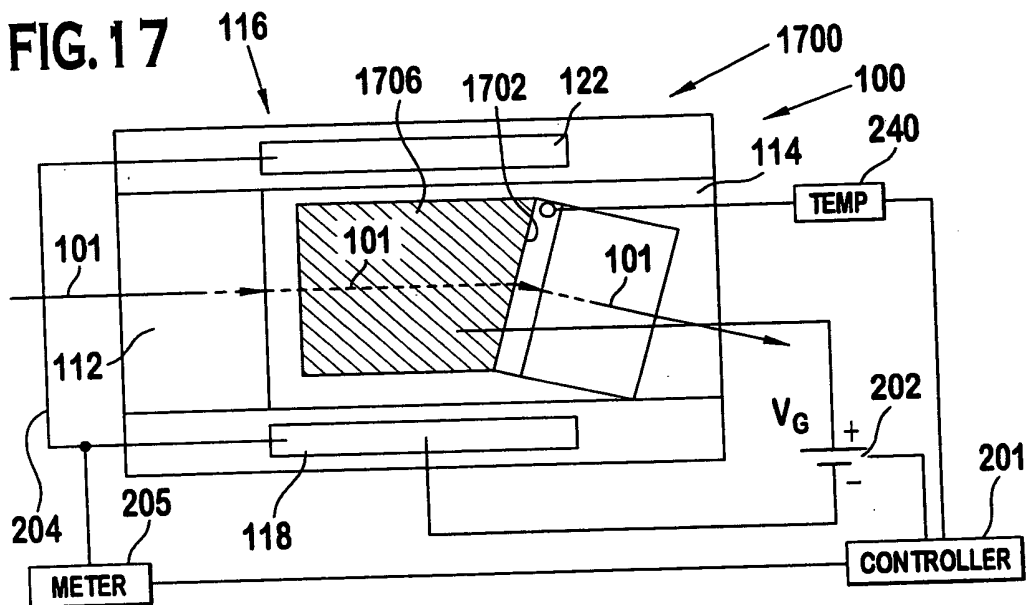
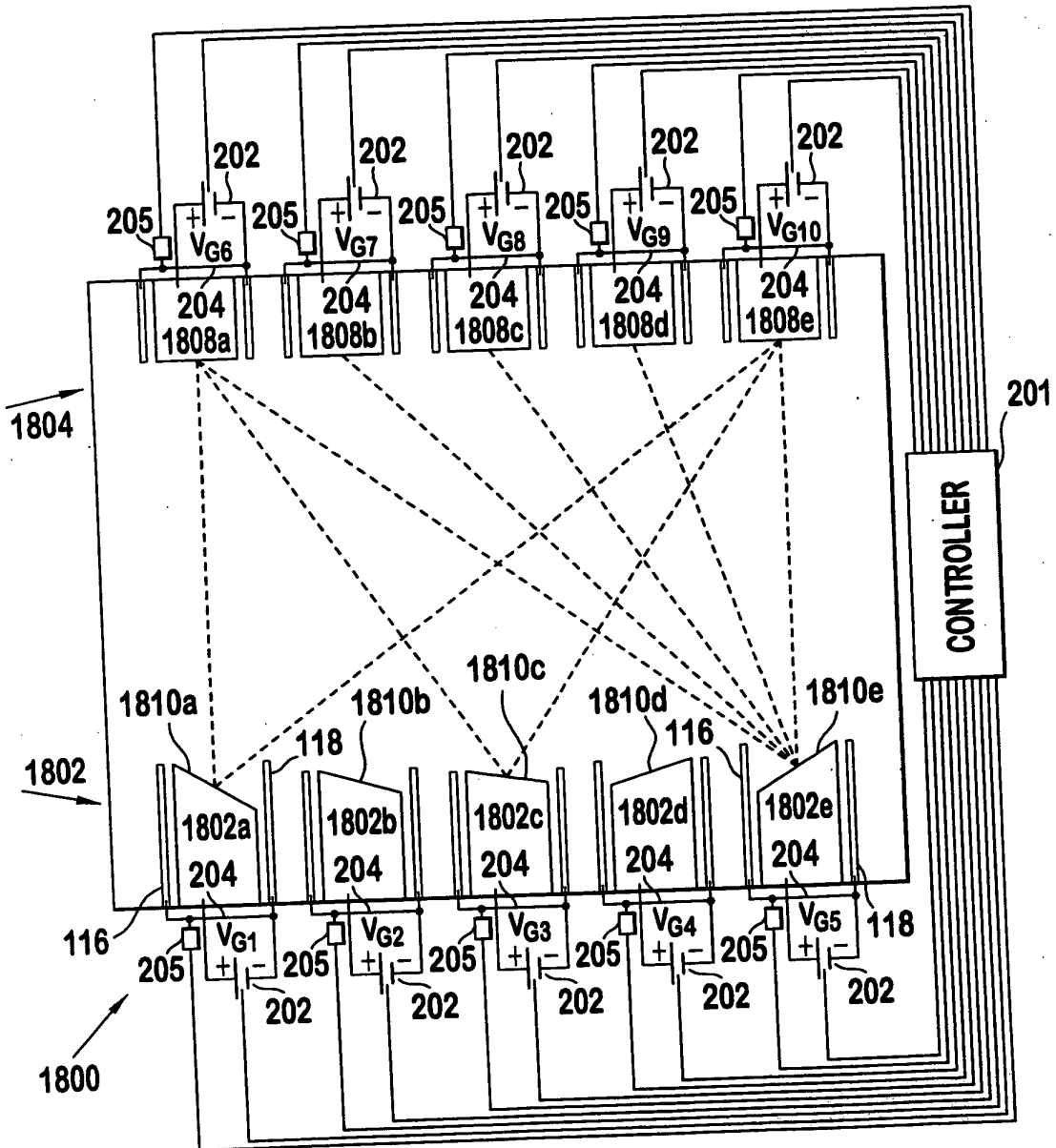


FIG. 17



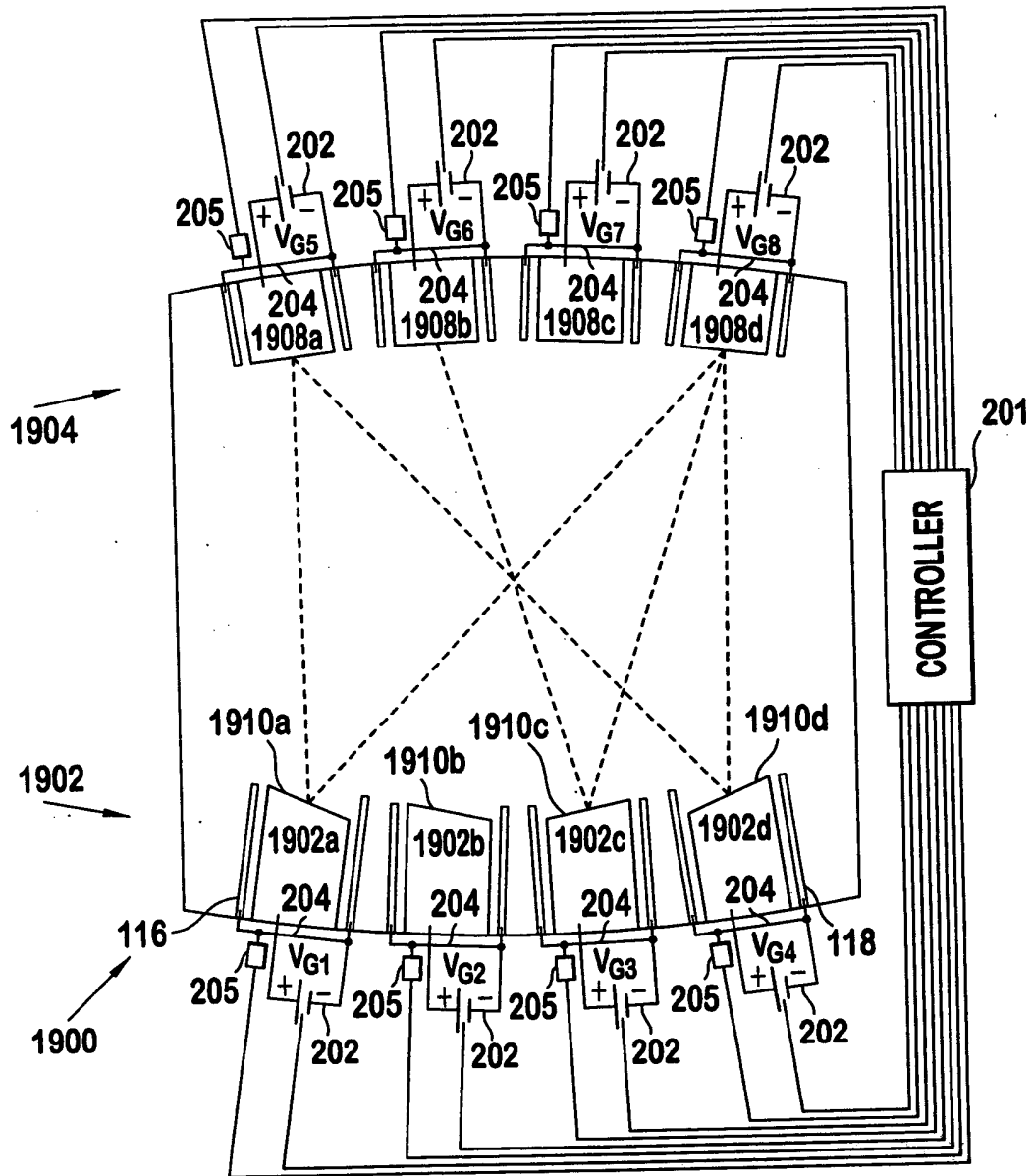
9/55

FIG. 18



10/55

FIG. 19



200220-89967001

FIG. 20

A cross-sectional view of a device. A top layer 120 is shown with a hatched pattern. Below it is a layer 110 containing a series of rectangular protrusions. The height of these protrusions is indicated by a double-headed arrow labeled T1. The distance between the centers of two adjacent protrusions is indicated by a double-headed arrow labeled d. A horizontal line 106 passes through the center of the protrusions. Below the protrusions is a layer 101. The thickness of layer 101 is indicated by a double-headed arrow labeled T2. The bottom surface of layer 101 is labeled 108. The entire structure is labeled 100. The protrusions are labeled 2002. The space between the protrusions is labeled 2004, 2006, 2010, and 2012. The label 2008 is also present.

[illegible]

FIG. 22

FIG. 22 is a cross-sectional view of a device assembly. A substrate 101 is shown with a top layer 110 and a bottom layer 106. A thin layer 120 is disposed on the top surface of layer 110. A series of small rectangular features 2202 are located on the top surface of layer 110, beneath layer 120. A series of small rectangular features 2212 are located on the top surface of layer 106, beneath layer 110. The device is shown in a perspective view with break lines indicating it is a partial view.

12/55

FIG. 23

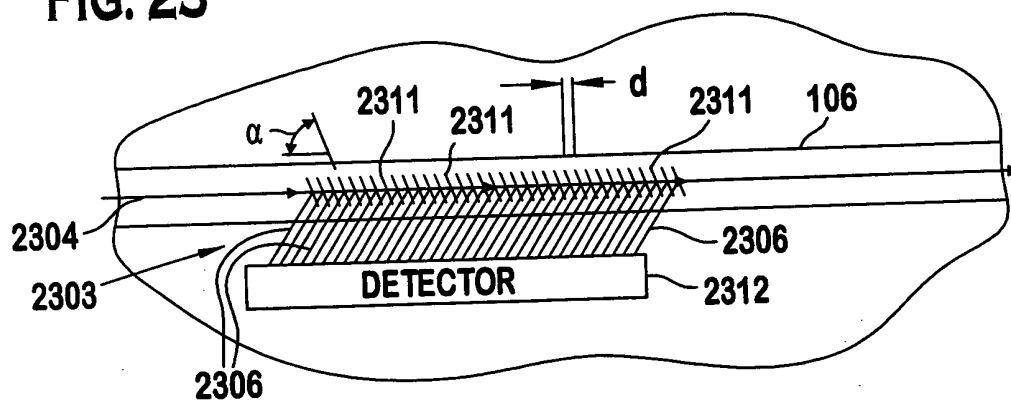
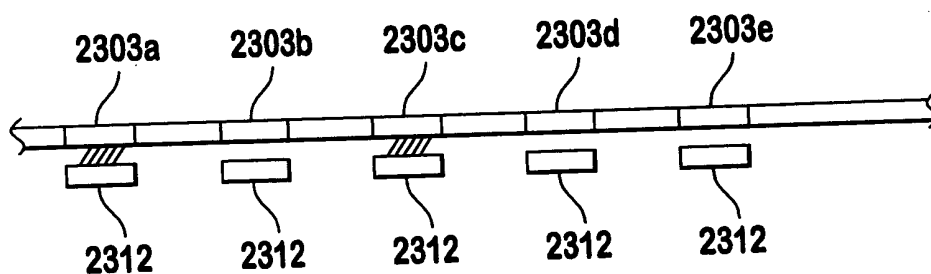


FIG. 24



13/55

FIG. 25

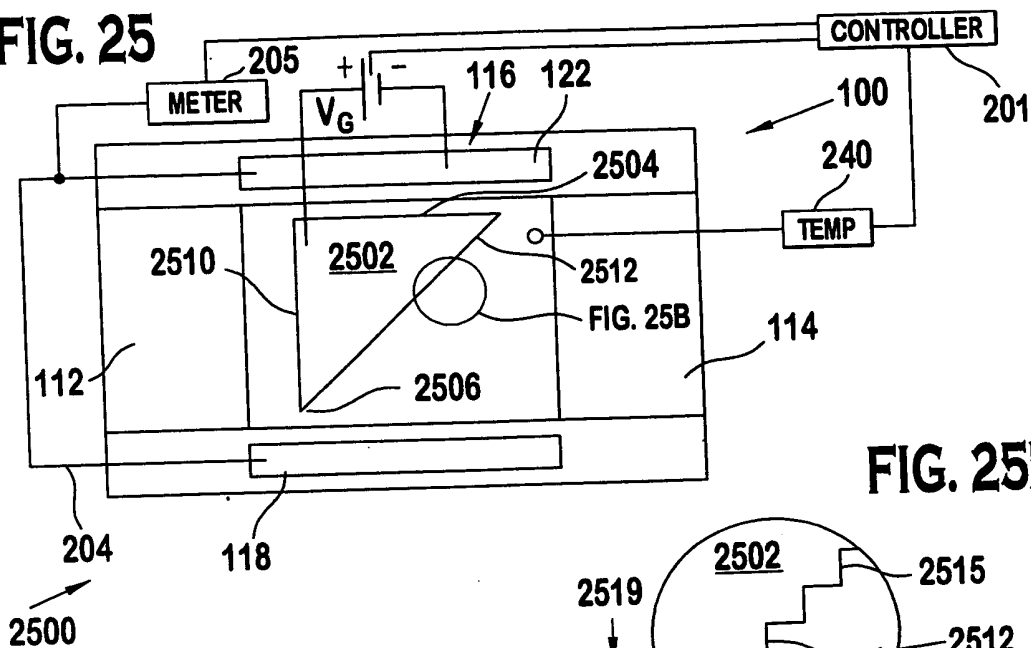


FIG. 25B

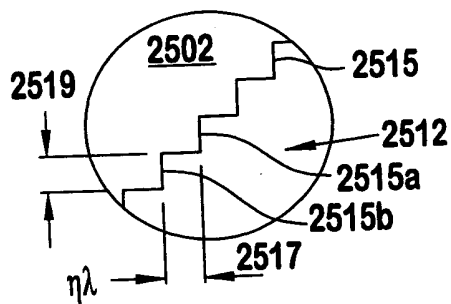
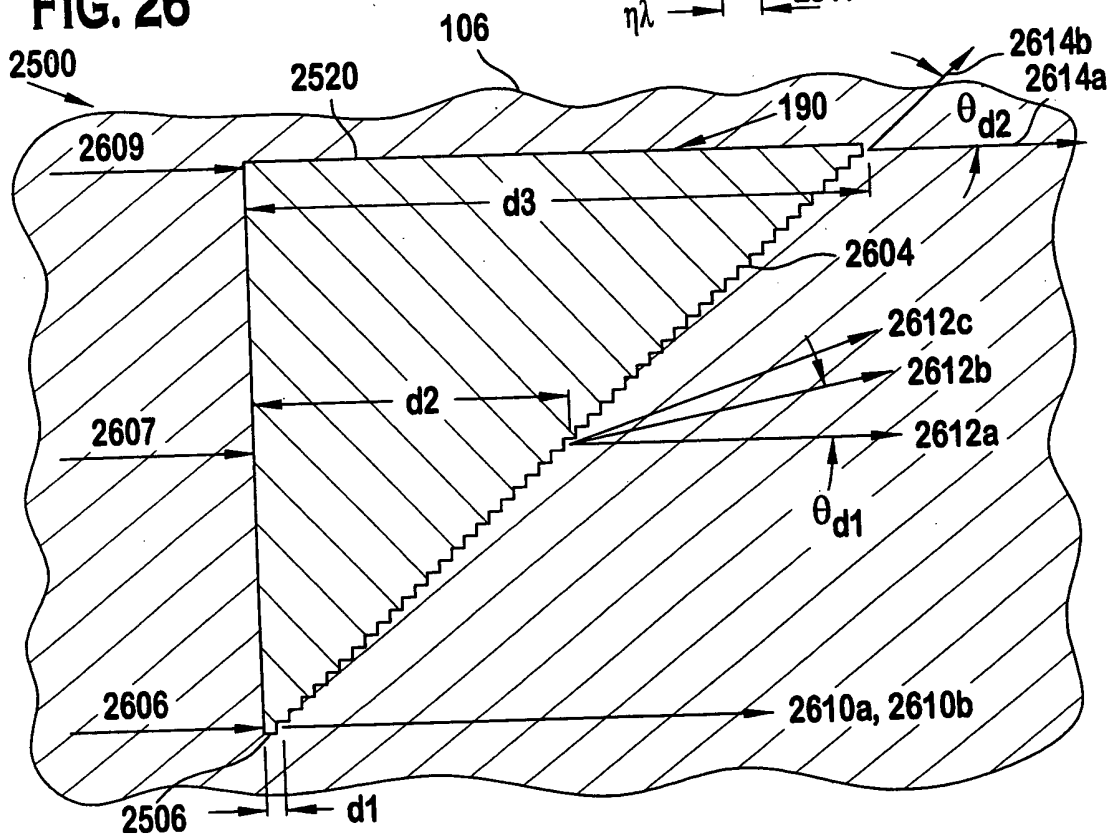


FIG. 26



200207-89964007

FIG. 28

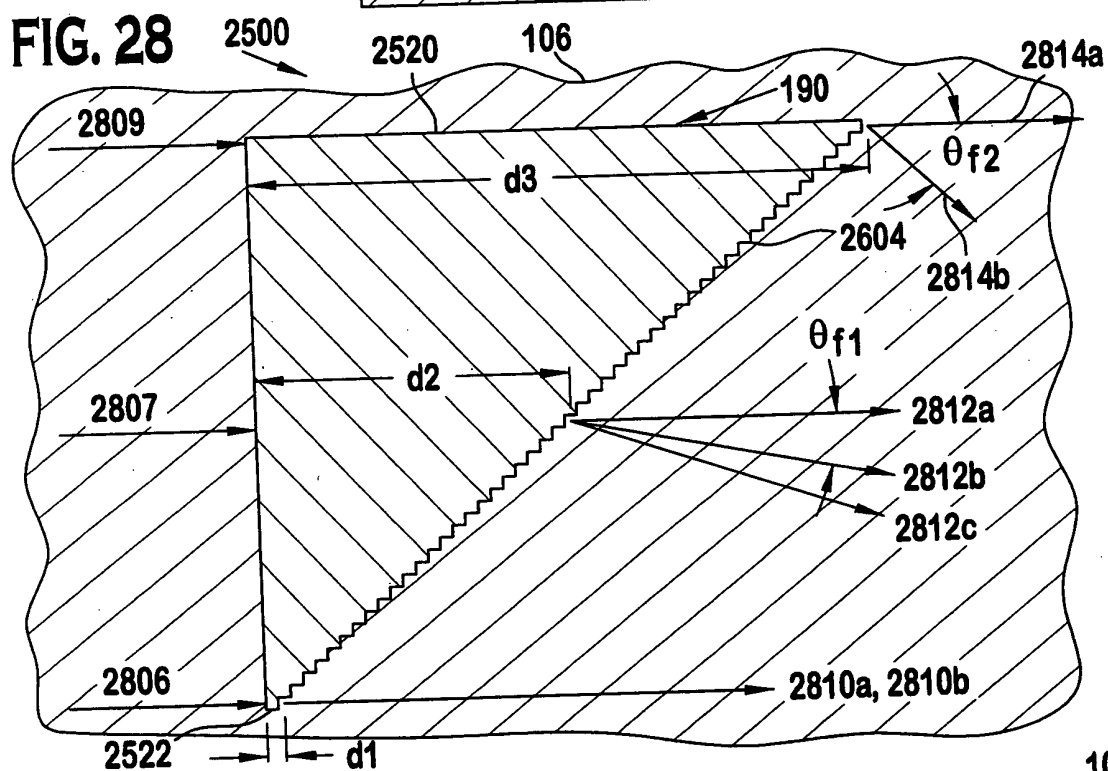
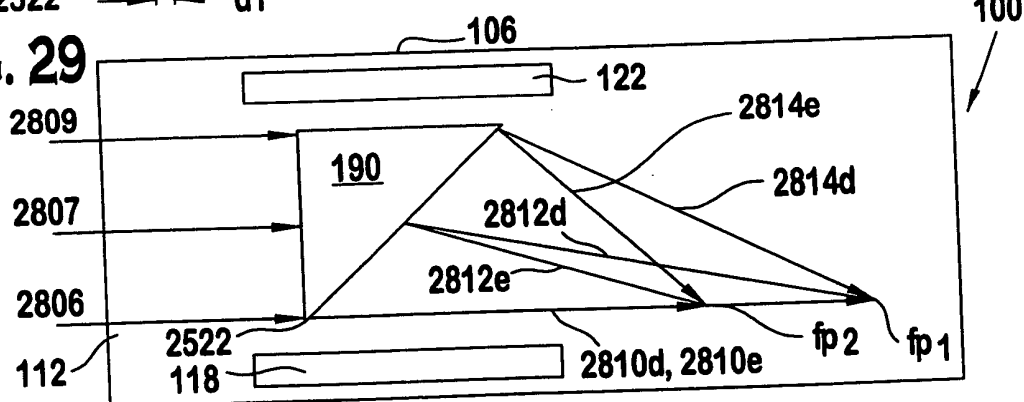


FIG. 29



[illegible]

Diagram illustrating a light source assembly 3008. The assembly includes a light source 3012a and a lens 3012b. A light beam 3014a/3014b is emitted from the lens and converges at a point 3016. The light beam is shown as a series of rays originating from the lens and converging at the point 3016. The lens 3012b is depicted as a vertical rectangular element with a series of horizontal lines, and the light source 3012a is shown as a series of horizontal lines. The light beam 3014a/3014b is represented by two lines diverging from the lens towards the point 3016.

16/55

FIG. 31

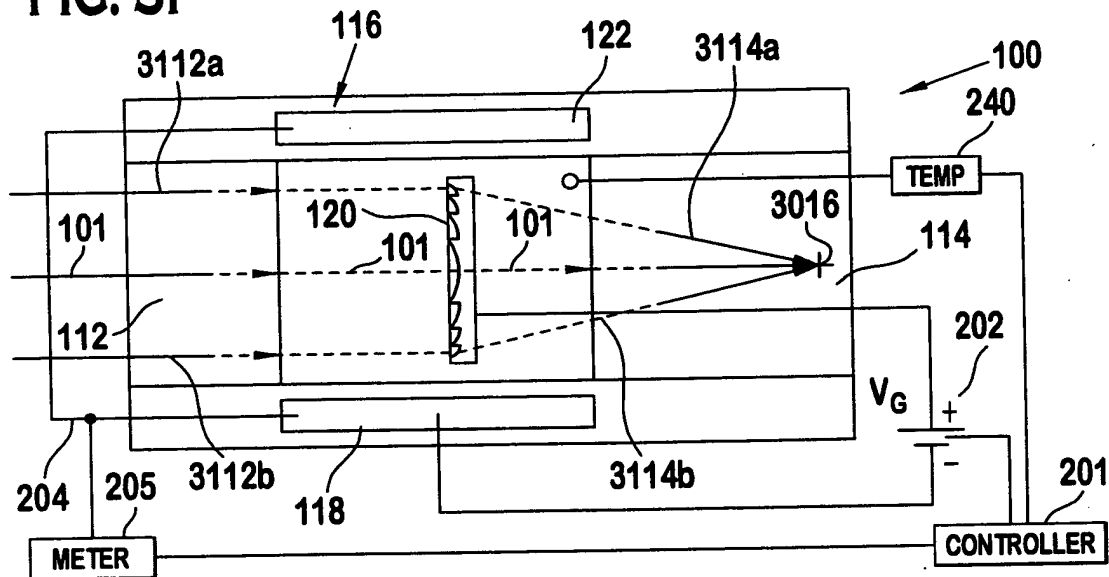
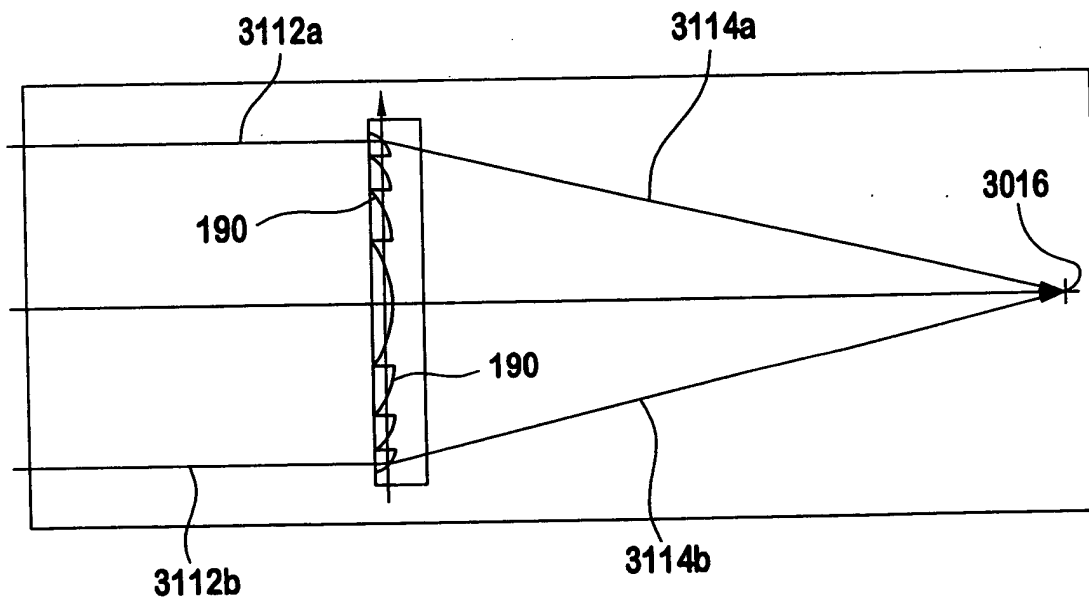


FIG. 31 A



200220-89967001

17/55

FIG. 32

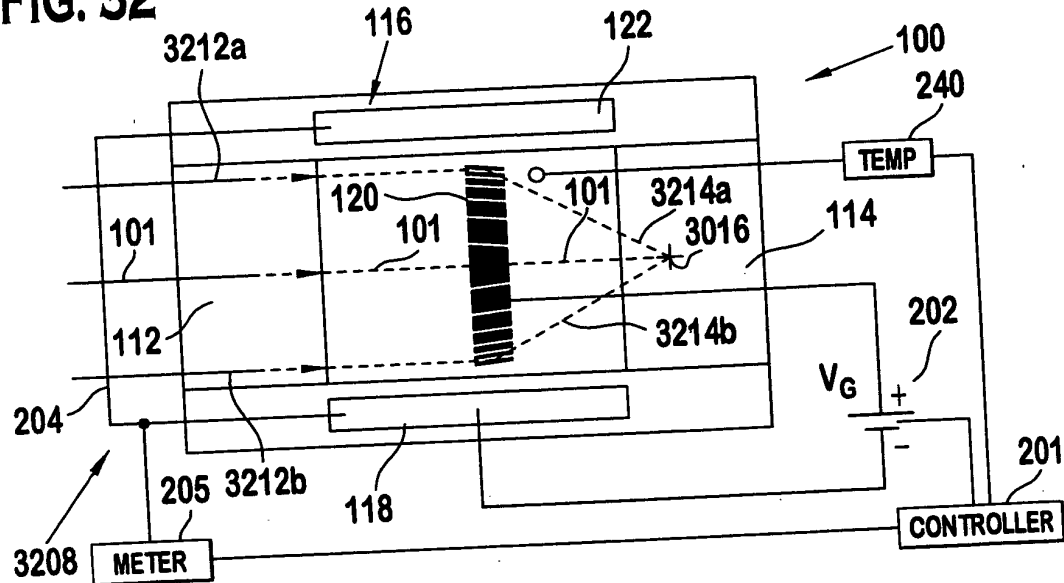
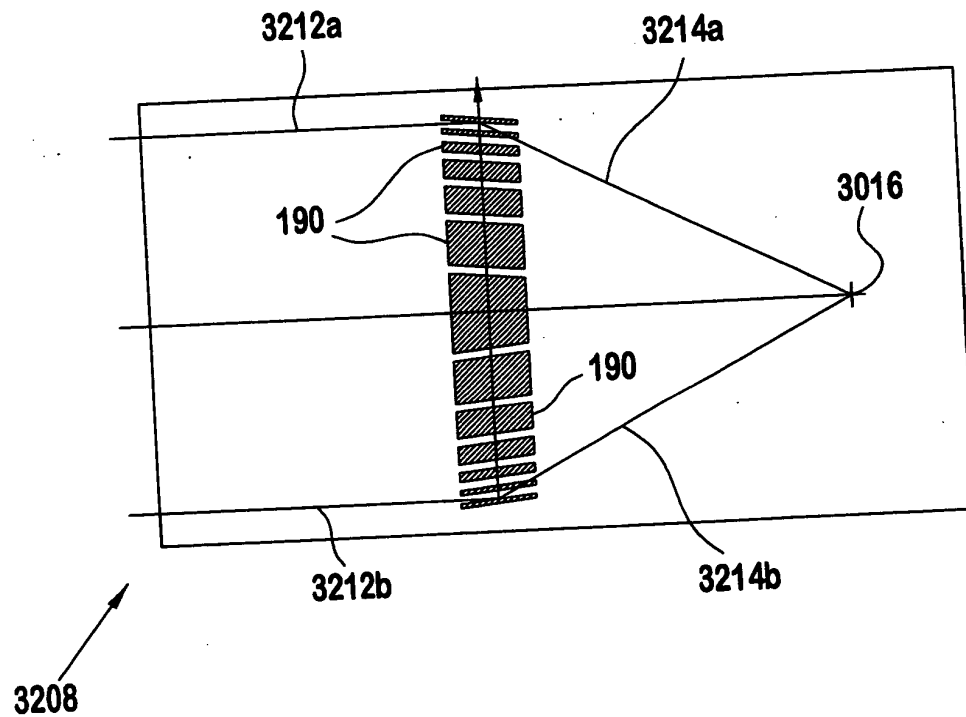


FIG. 32A



18/55

FIG. 33

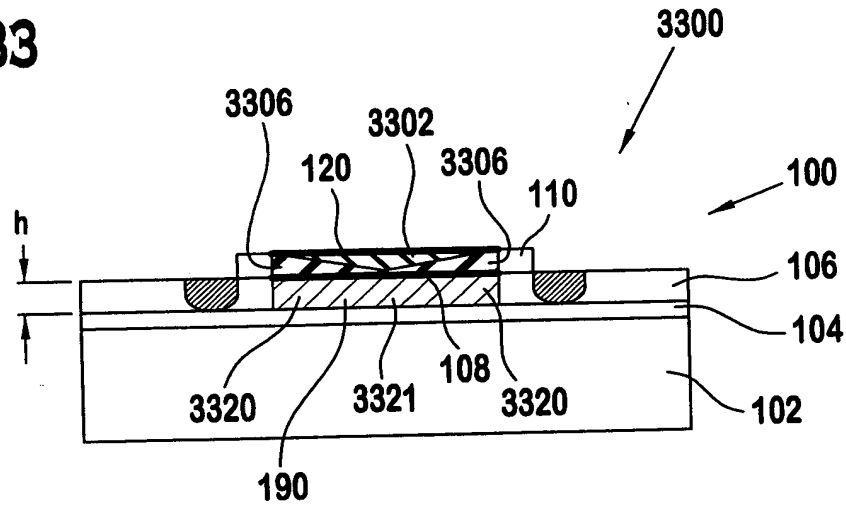
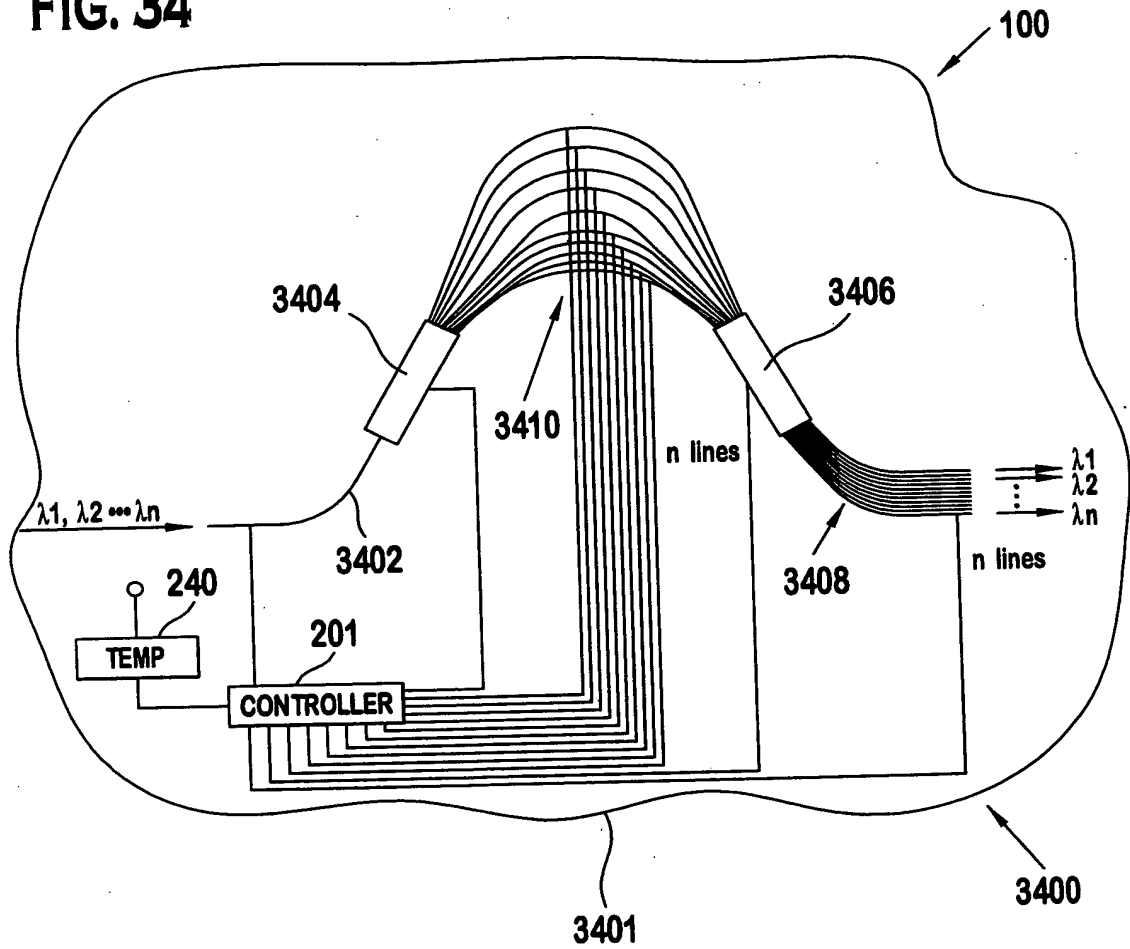


FIG. 34



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200220-8996/001

FIG. 37

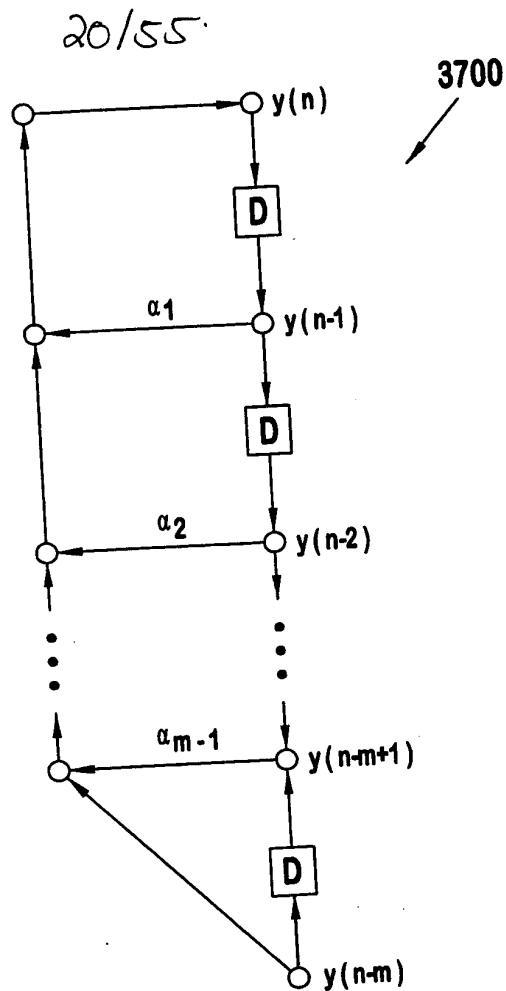
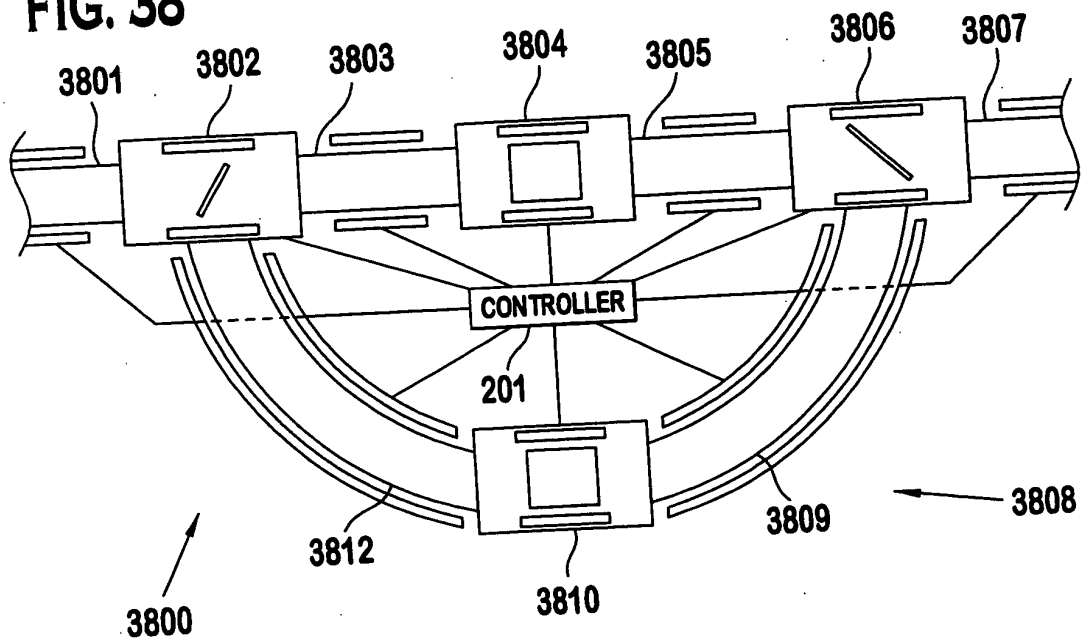
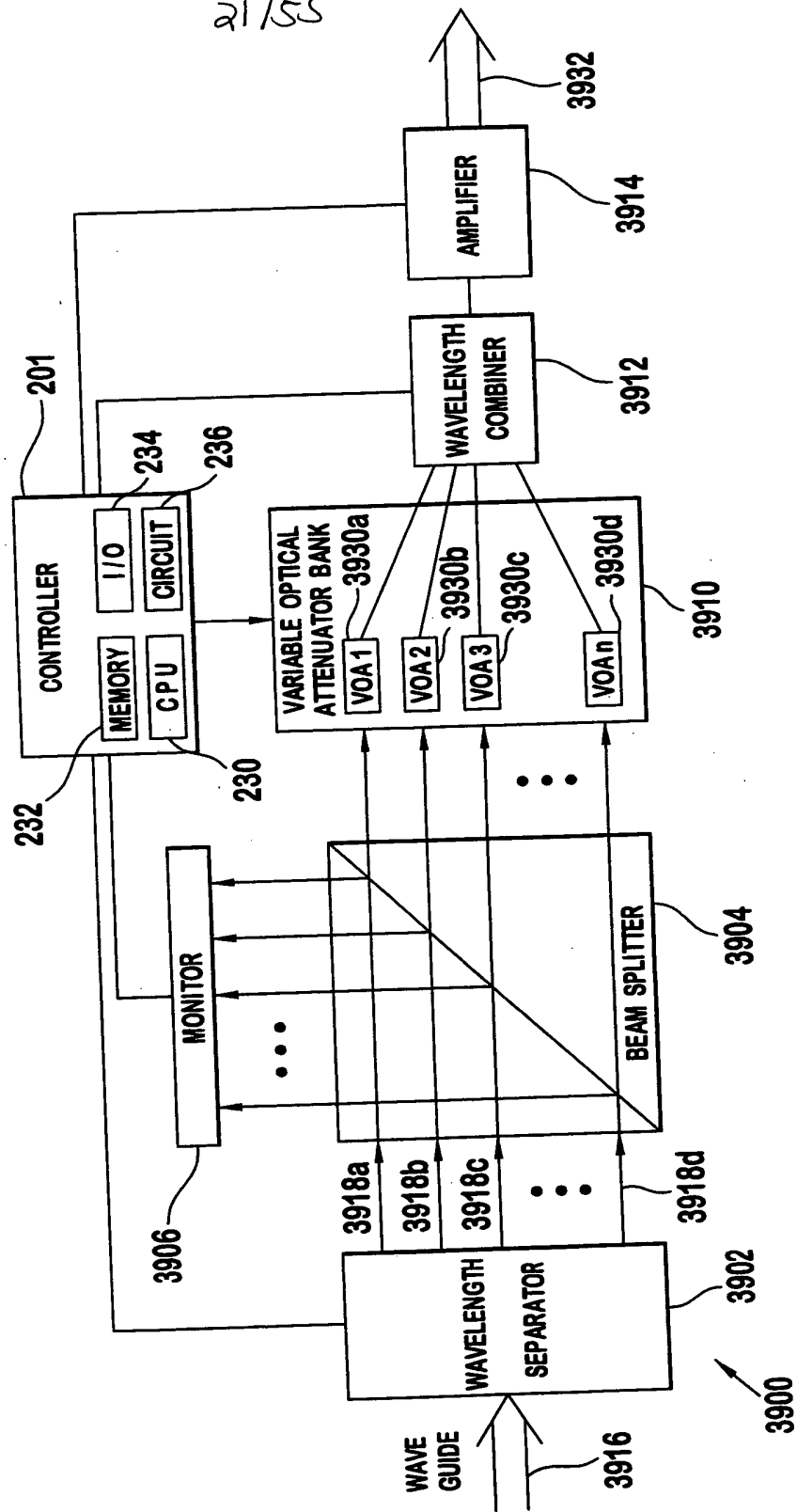


FIG. 38



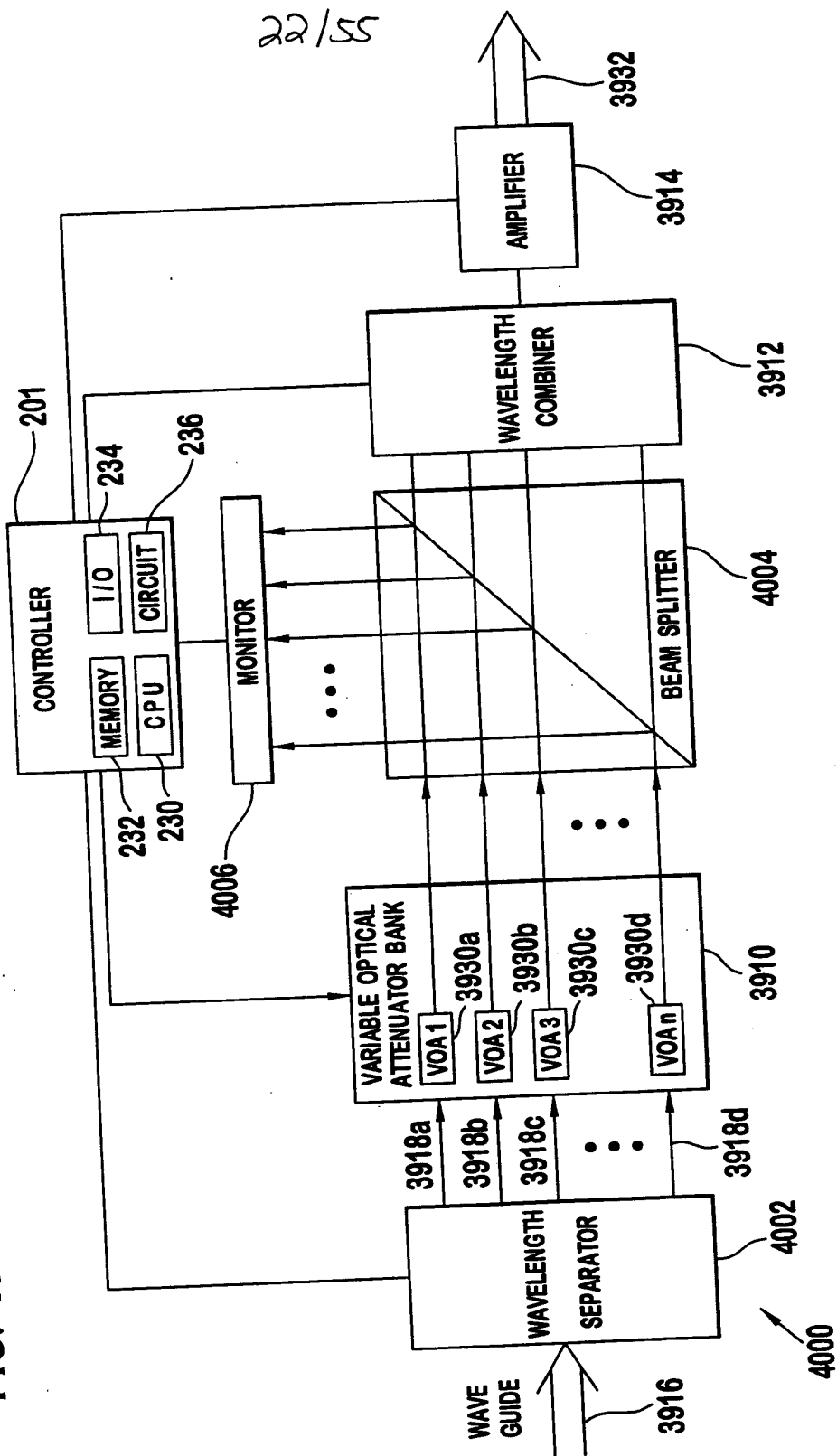
21/55

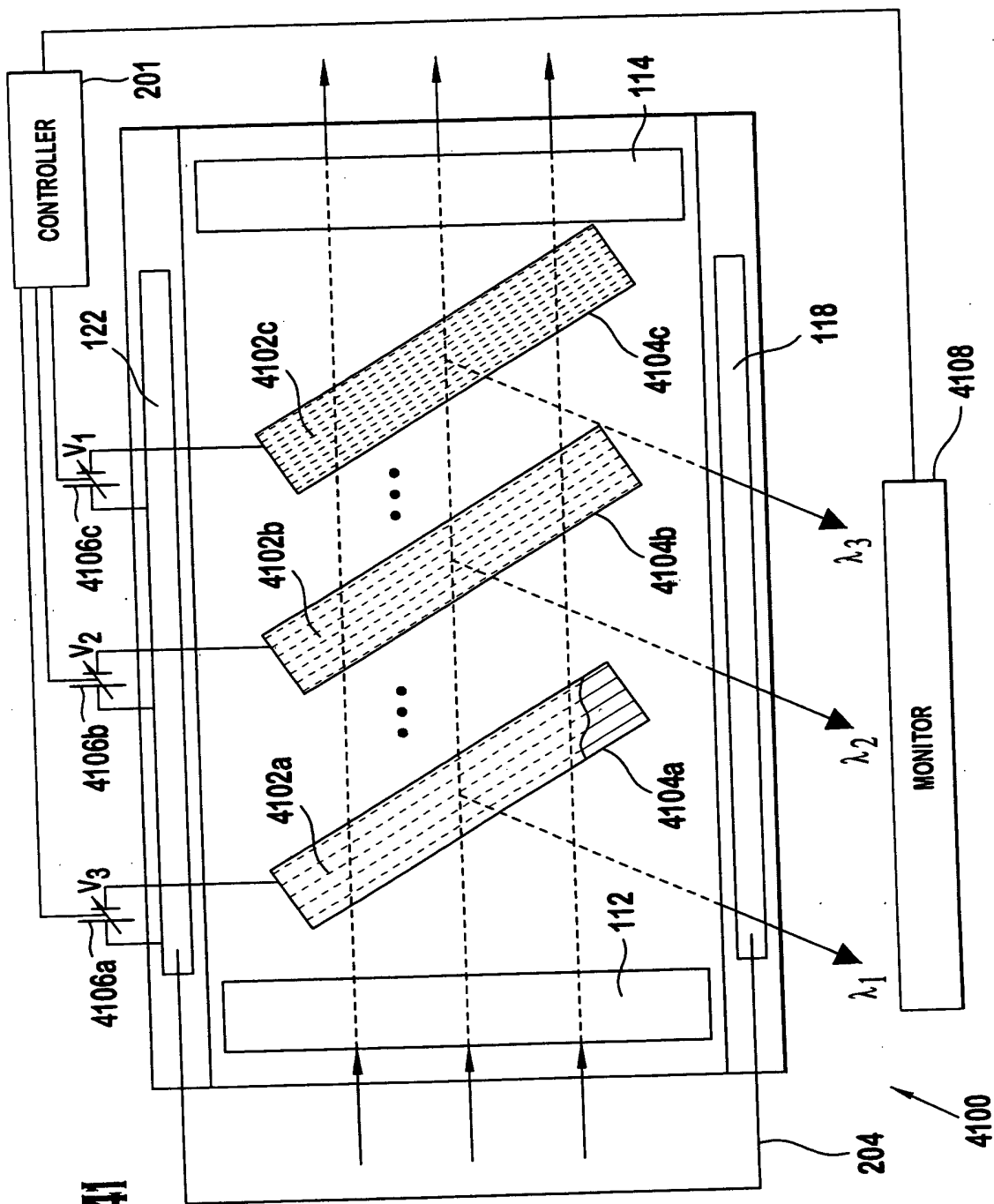
FIG. 39



22/55

FIG. 40





24/55

FIG. 42

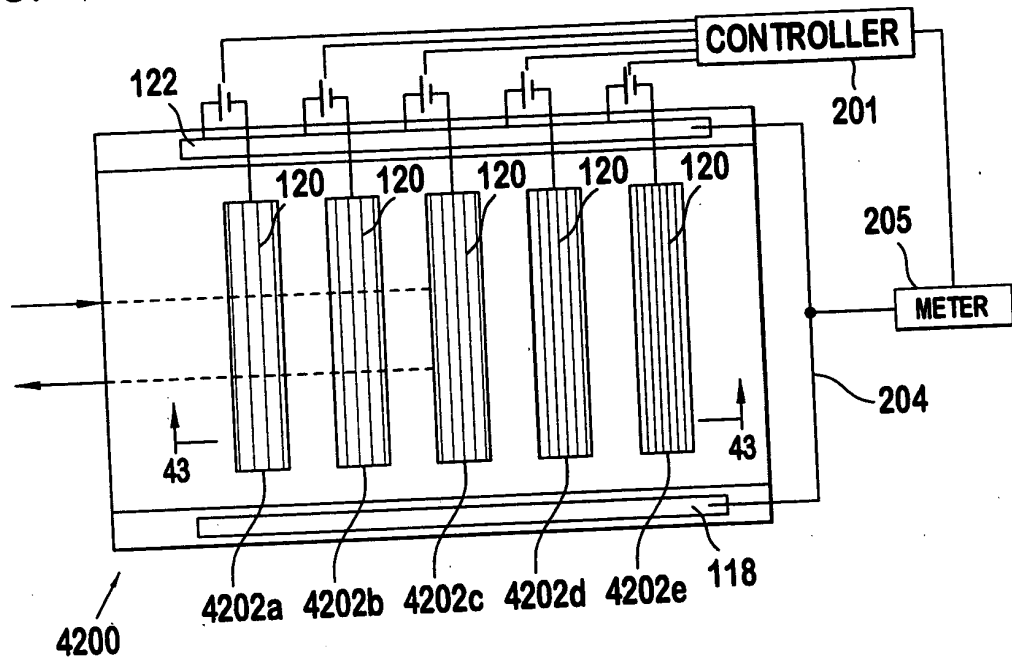
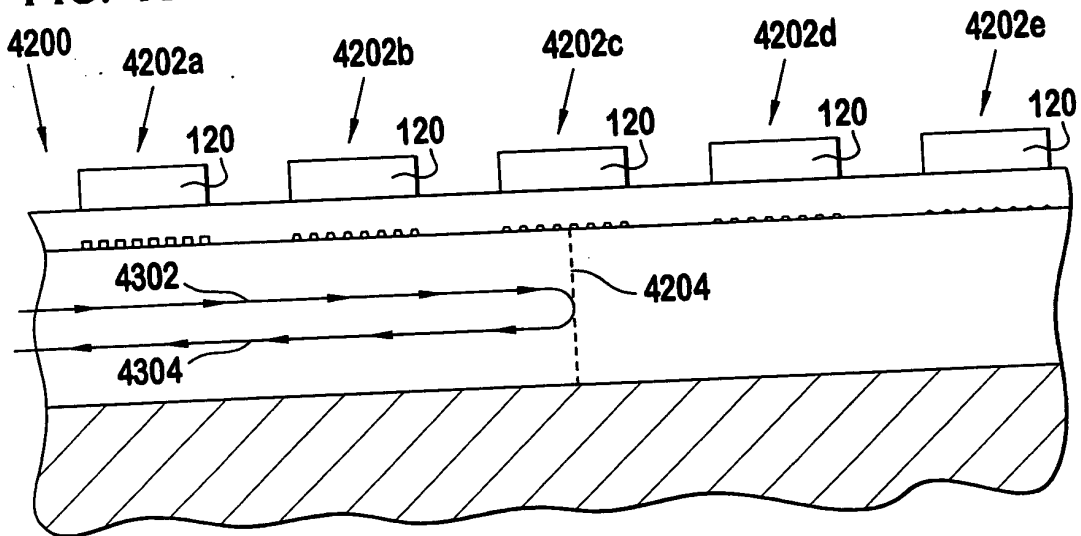
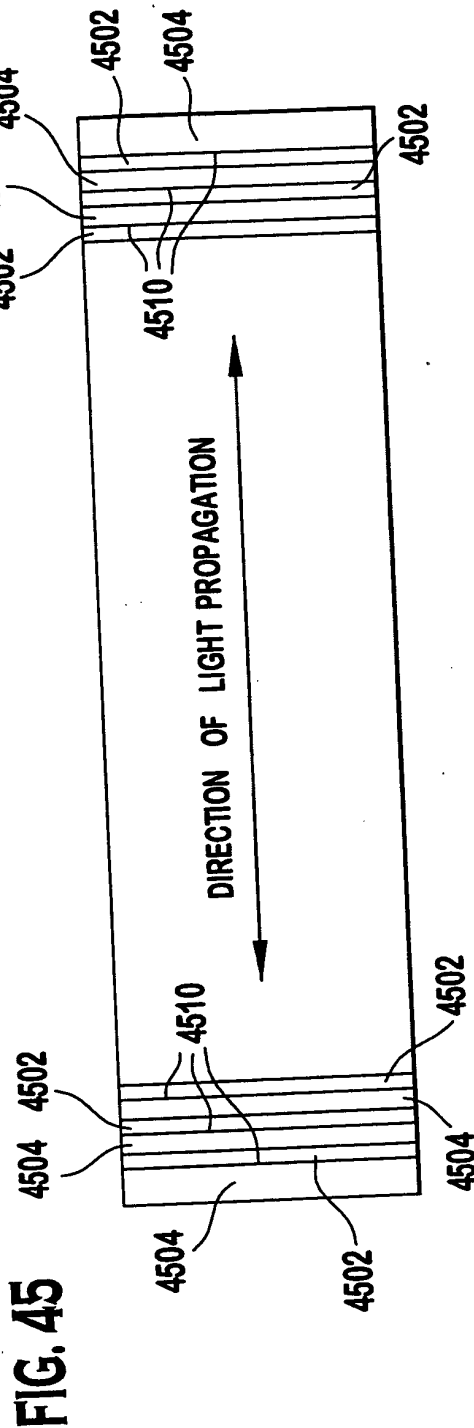
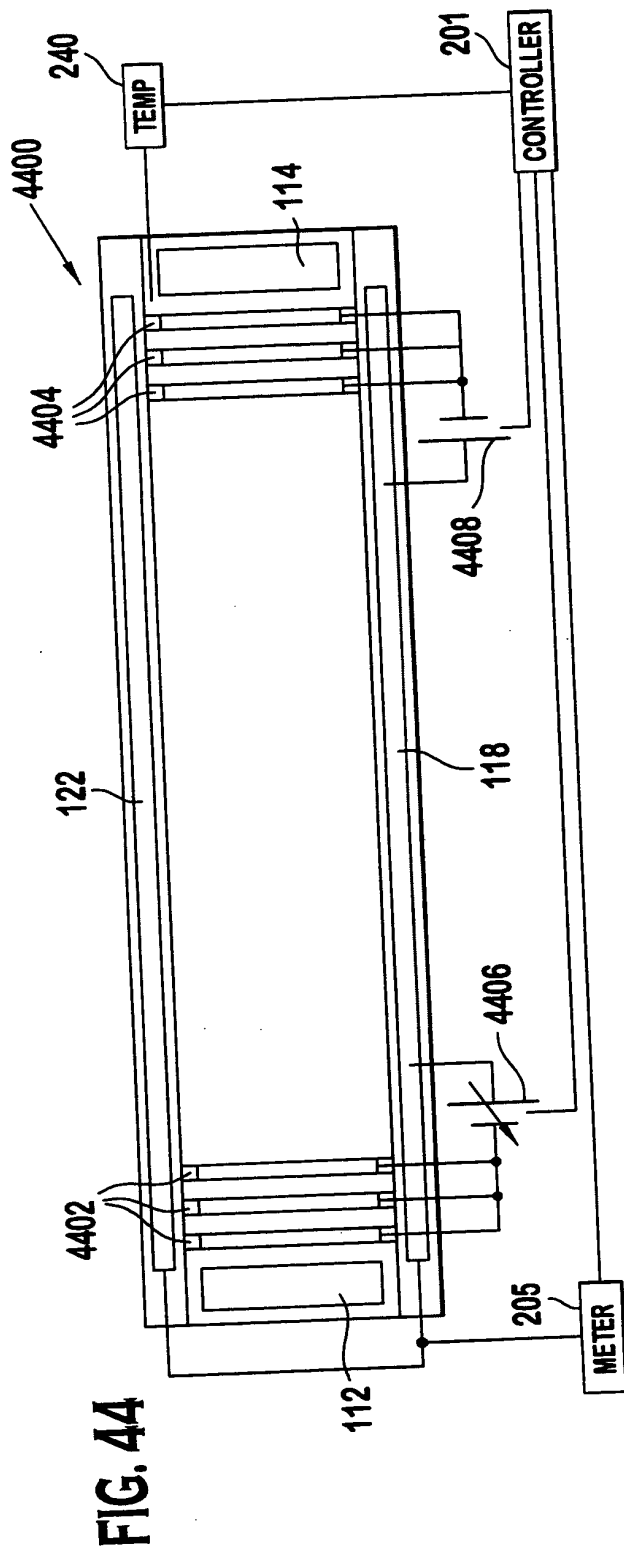


FIG. 43

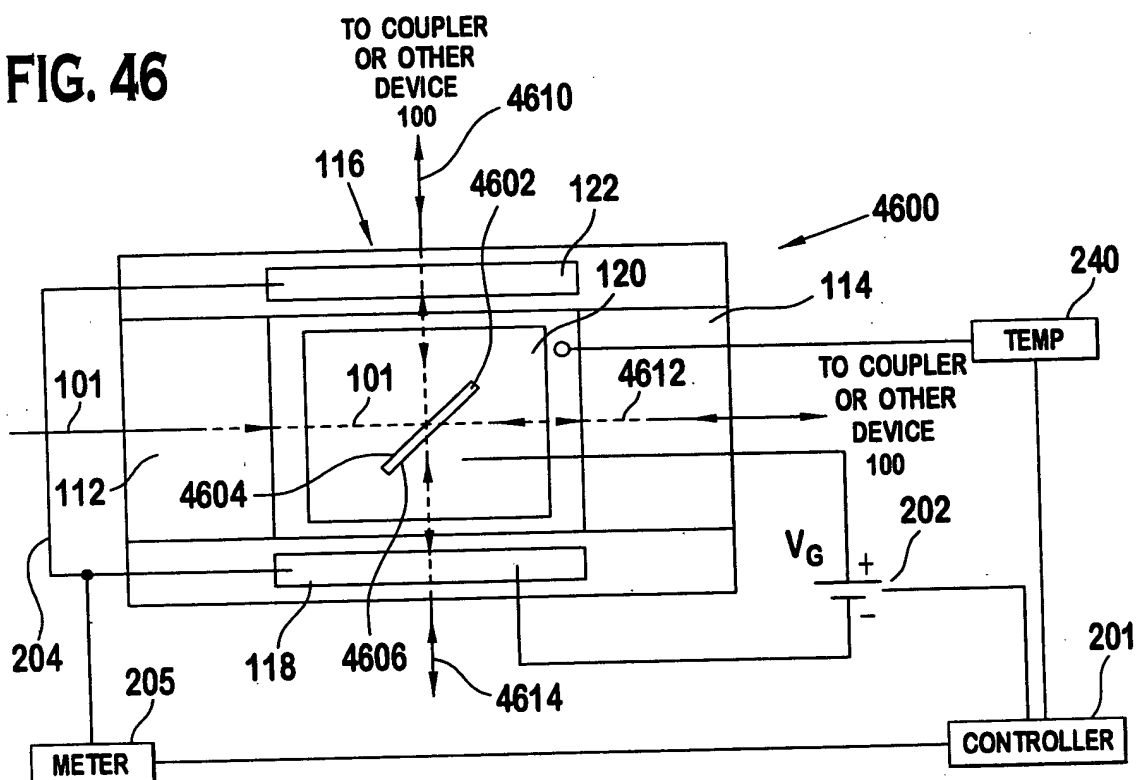


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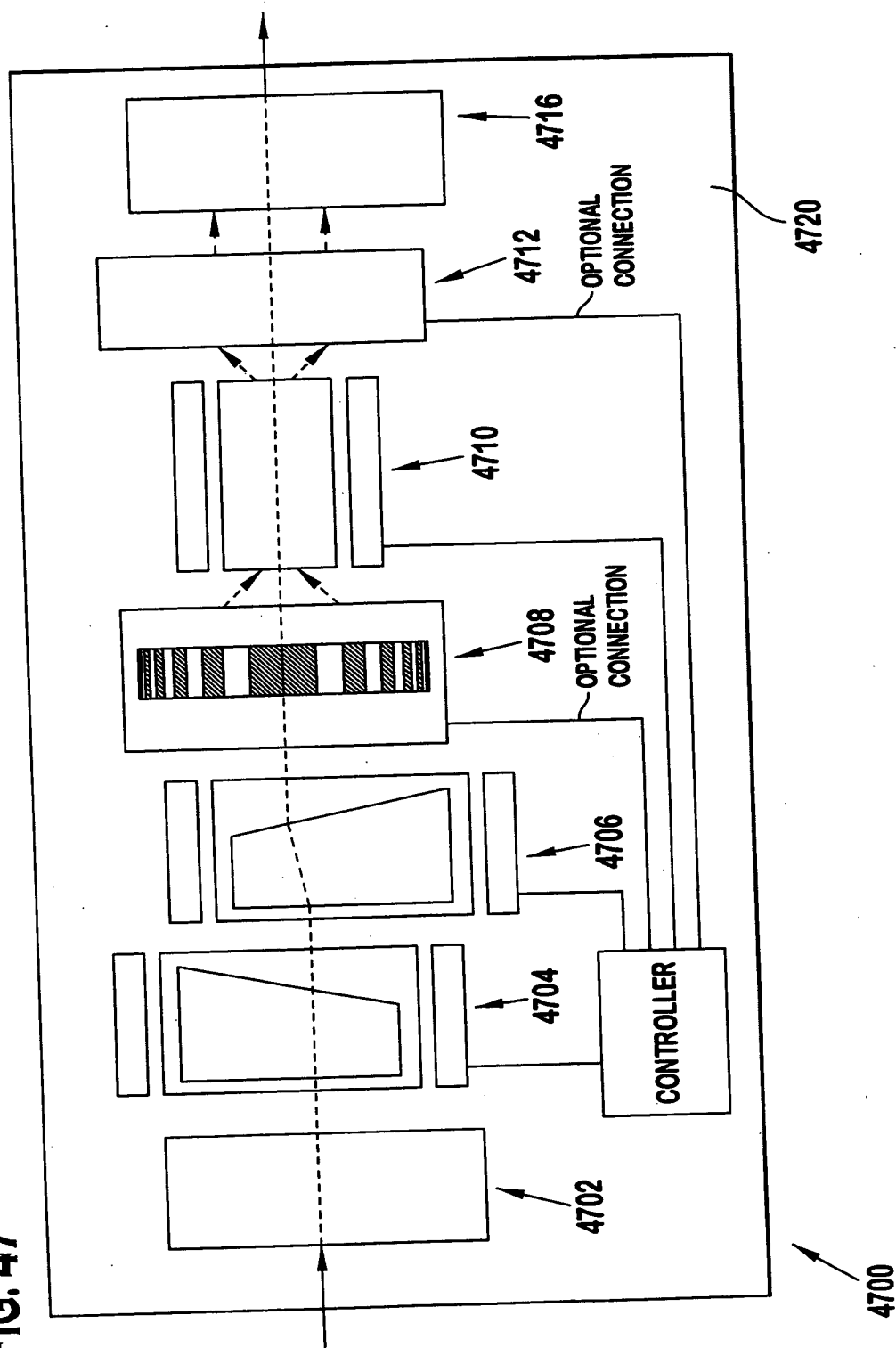
26/55

FIG. 46



27/55

FIG. 47



28/55

FIG. 48

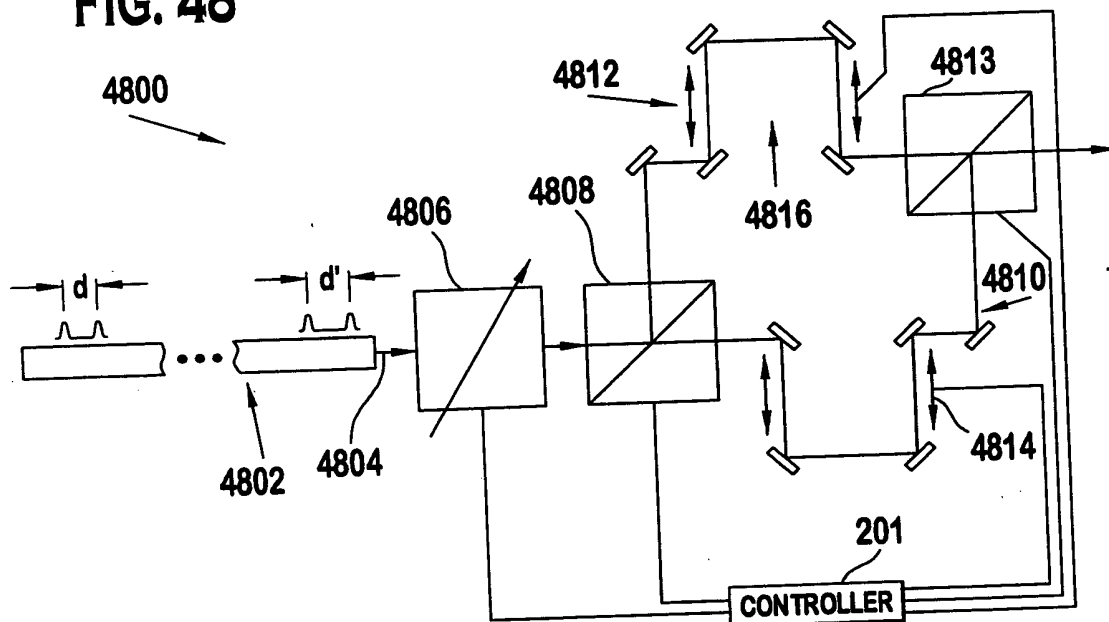
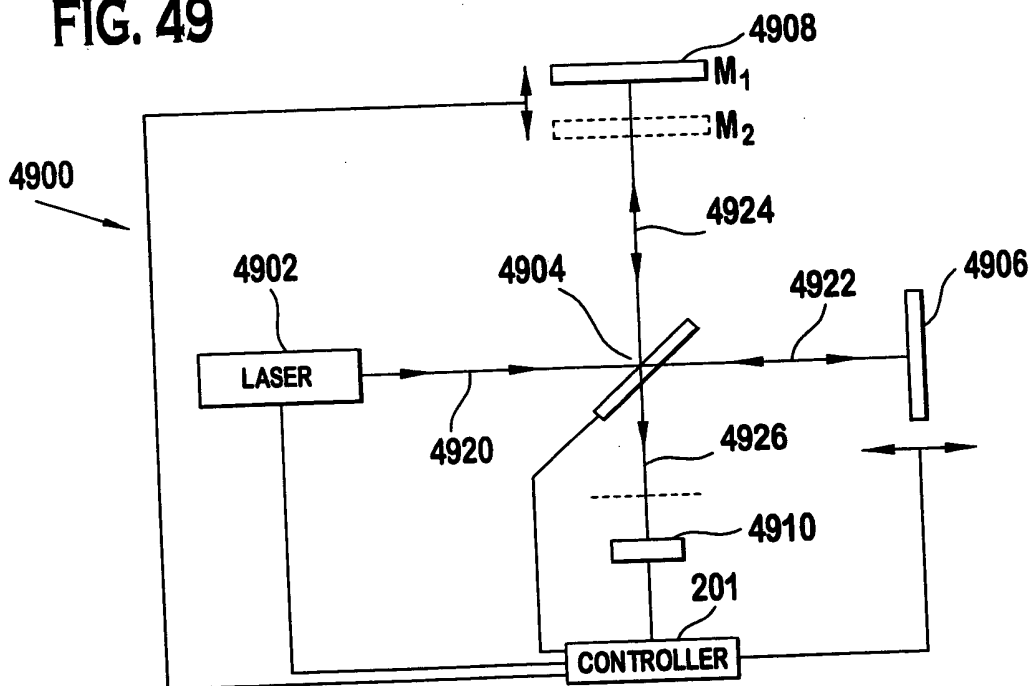


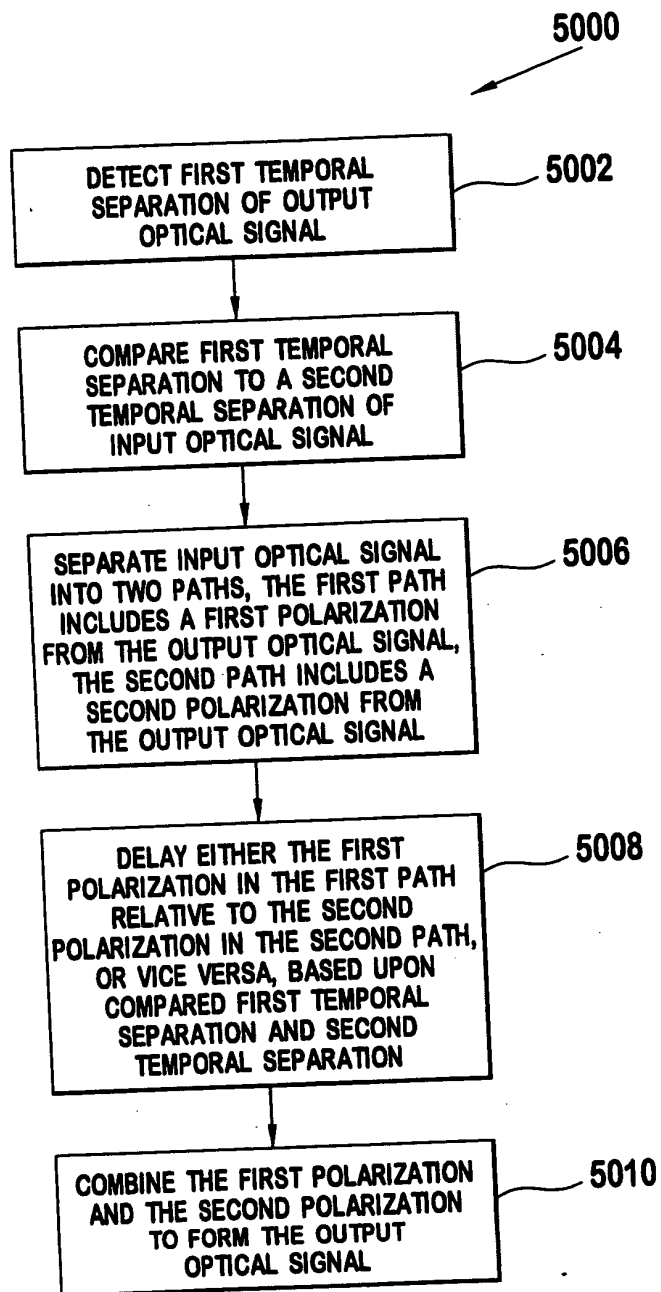
FIG. 49



200207-89967007

29/55

FIG. 50



10079668-023002

30/55

FIG. 51

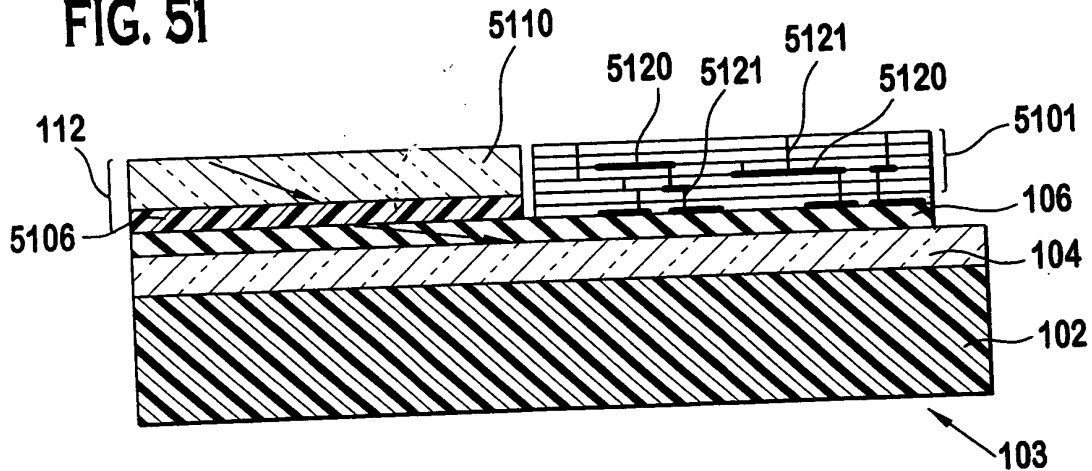
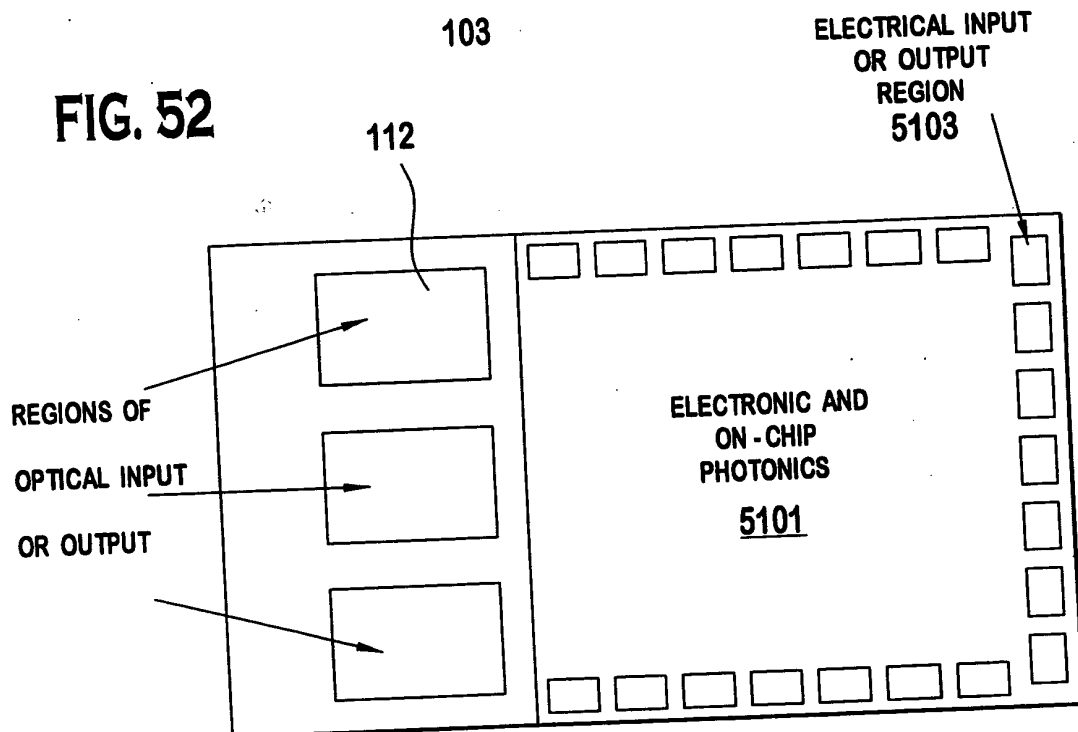


FIG. 52



31/55

FIG. 53

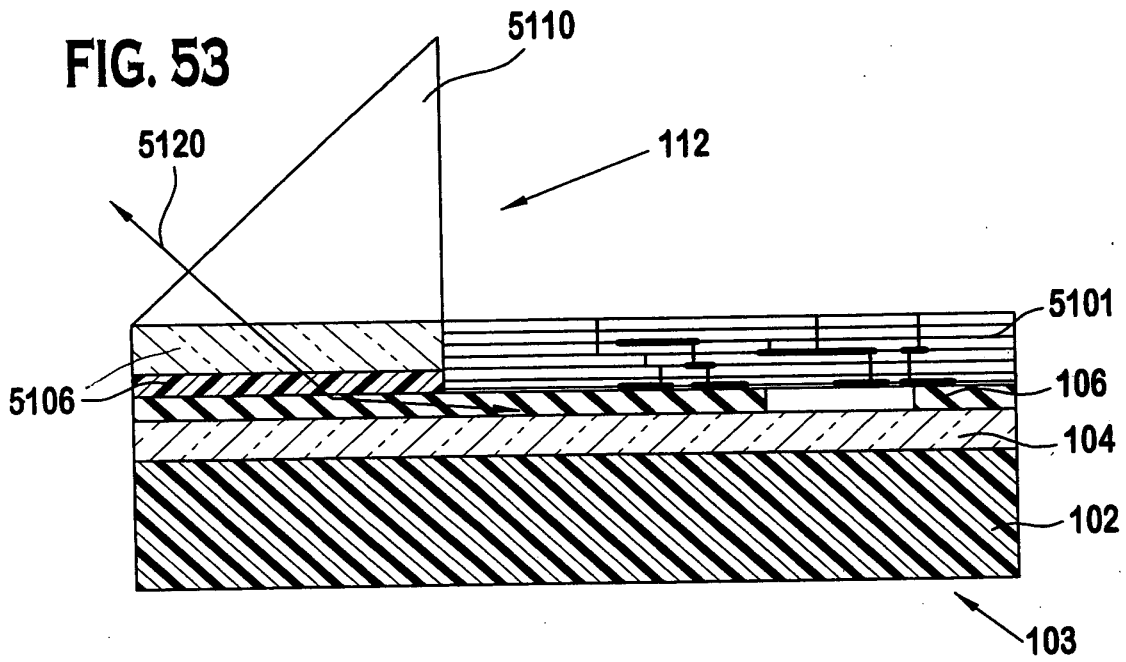
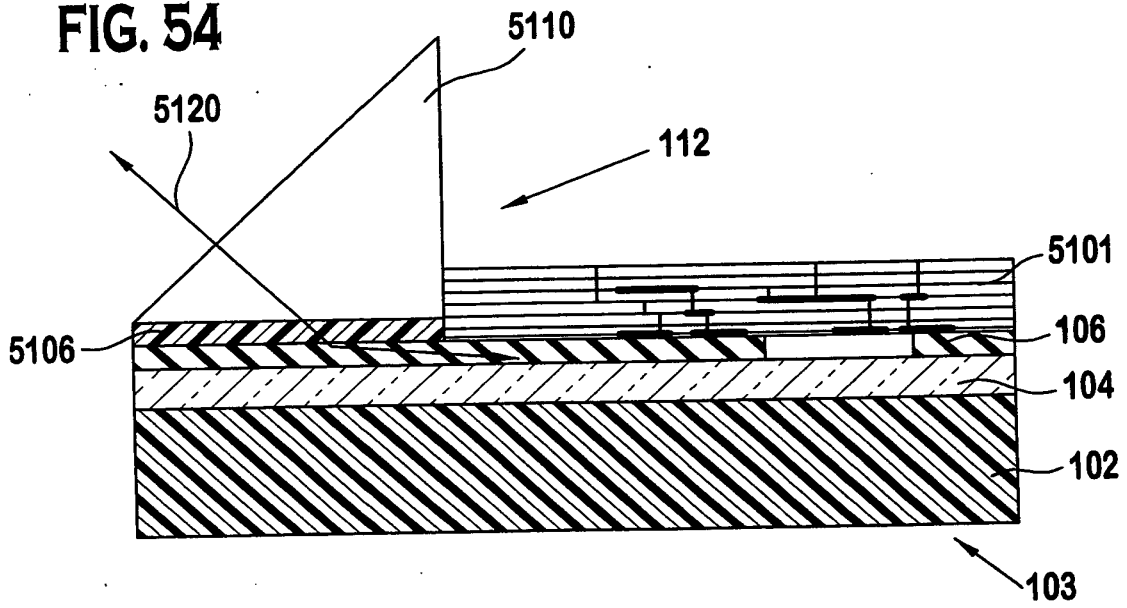


FIG. 54



200220.89967001

FIG. 55

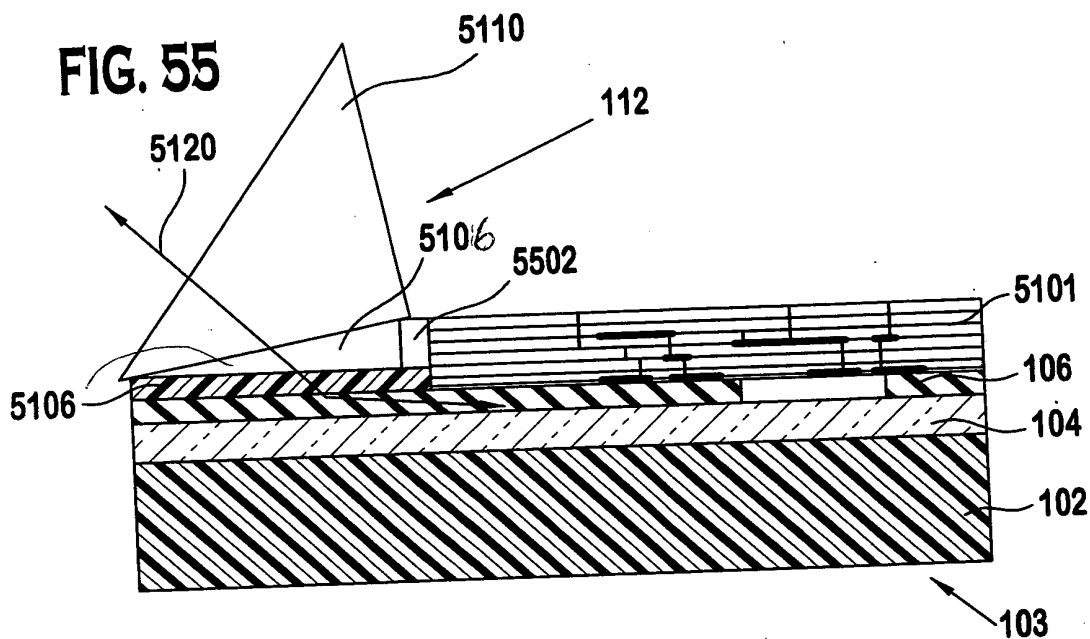
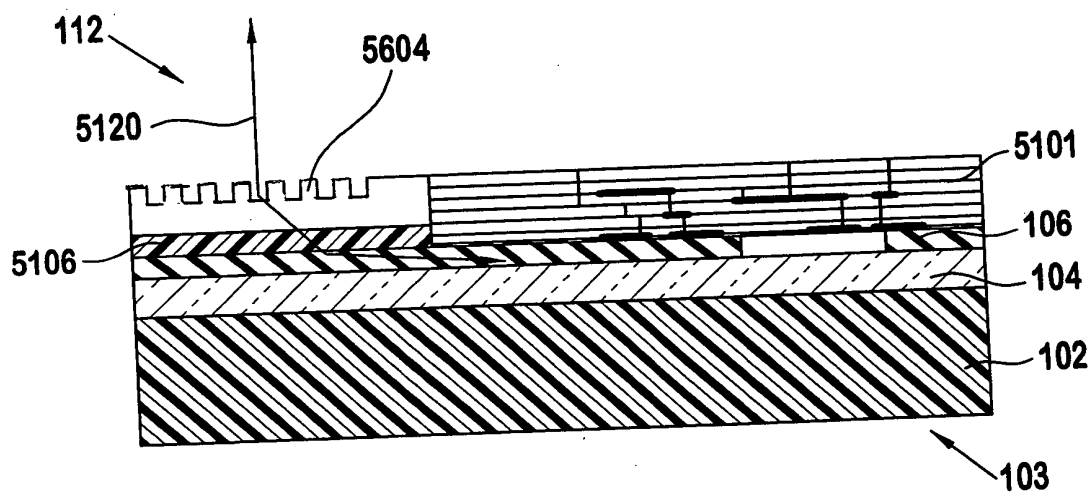


FIG. 56



200220-89967001

FIG. 57

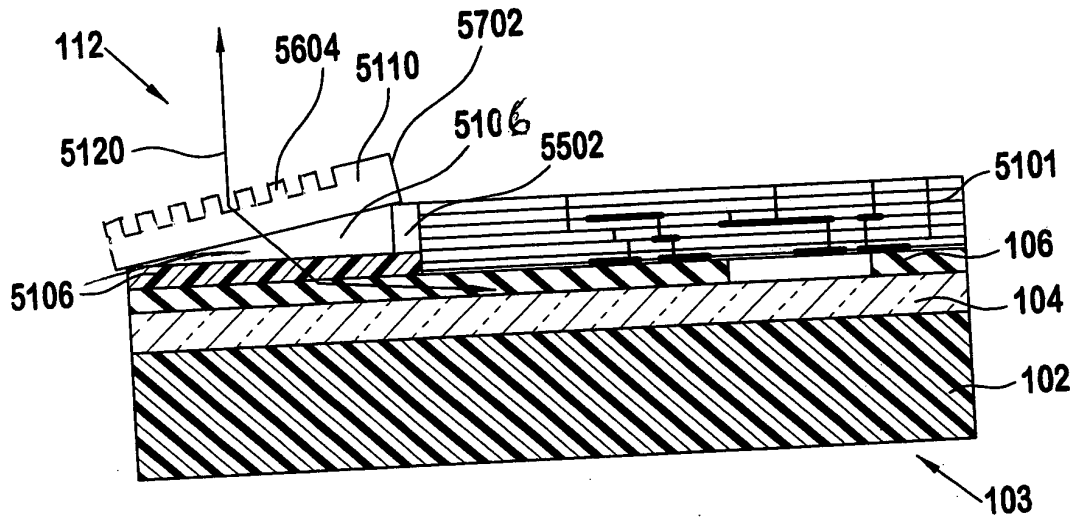
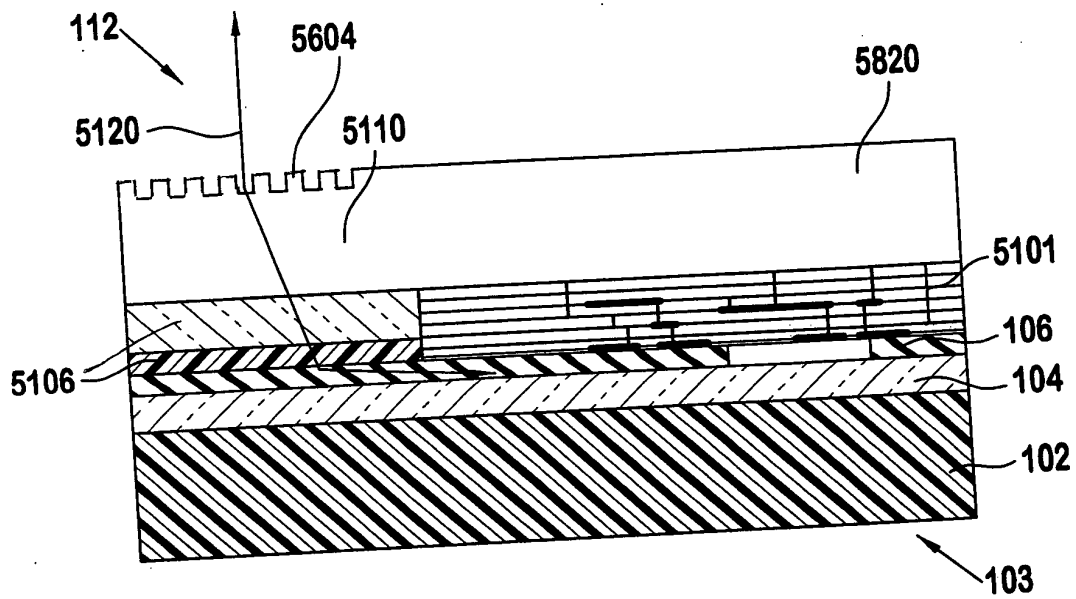


FIG. 58



200220 89964001

34/55

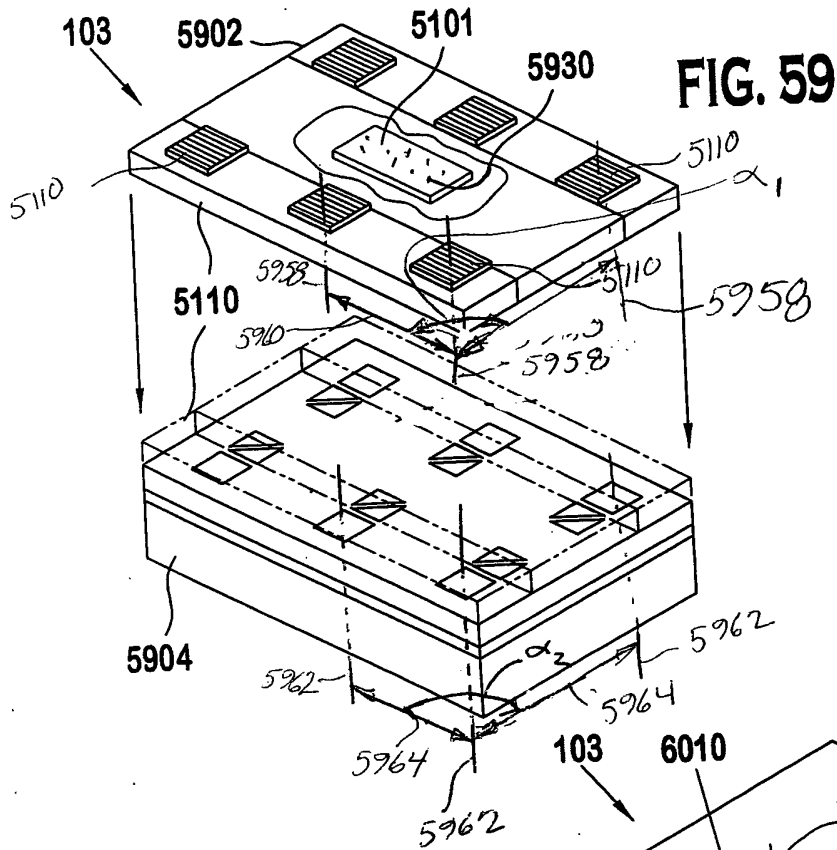


FIG. 59

FIG. 60

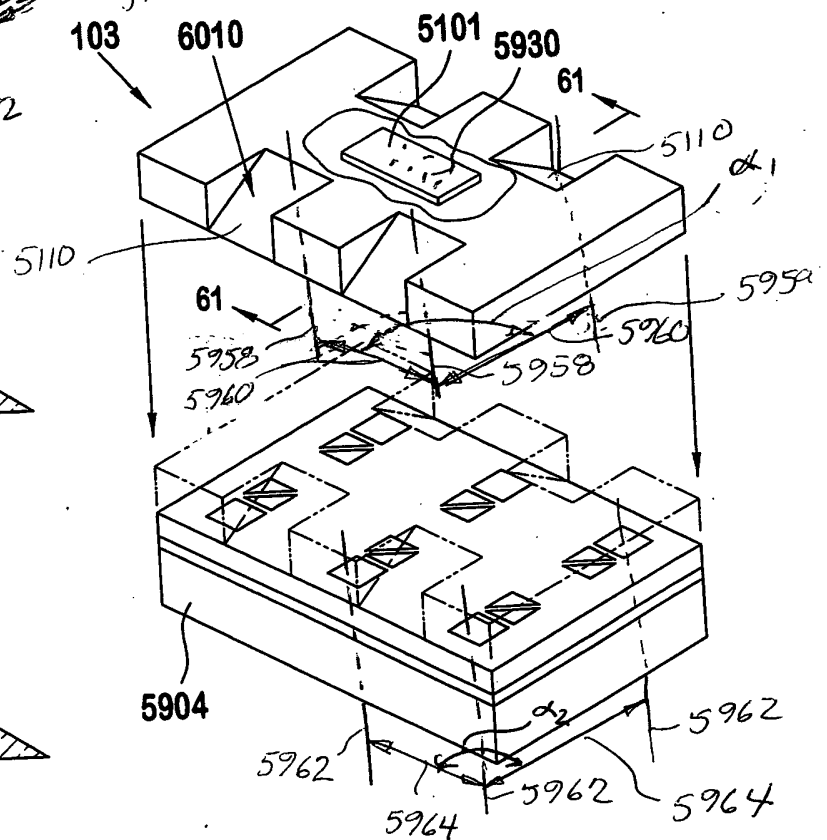


FIG. 61

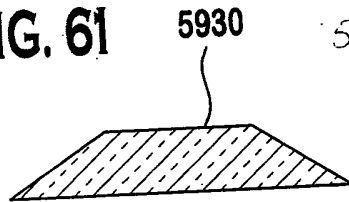
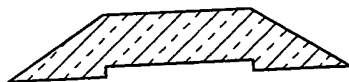


FIG. 62



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FIG. 63A

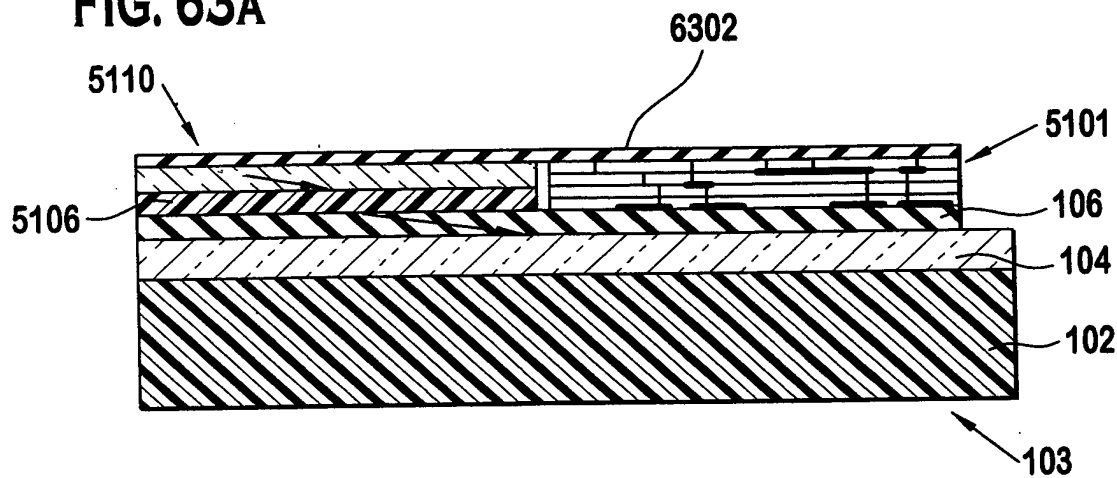
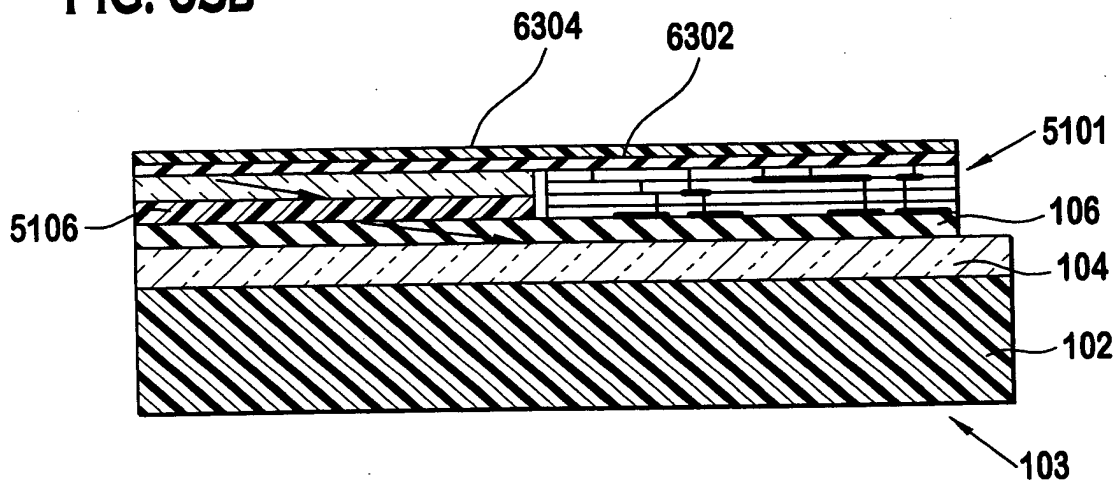


FIG. 63B



36/55

FIG. 63C

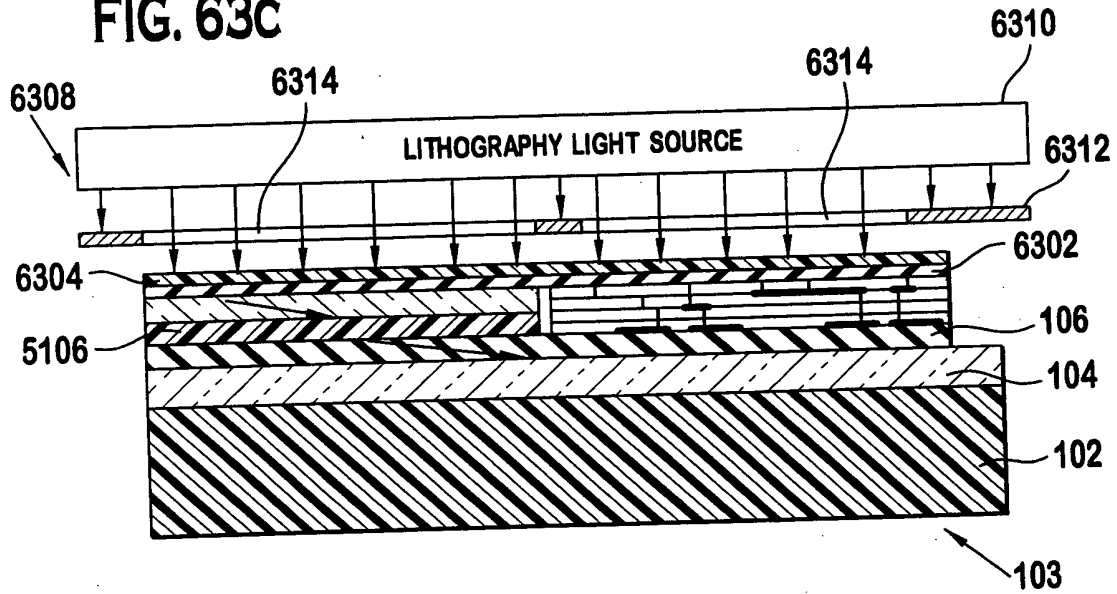
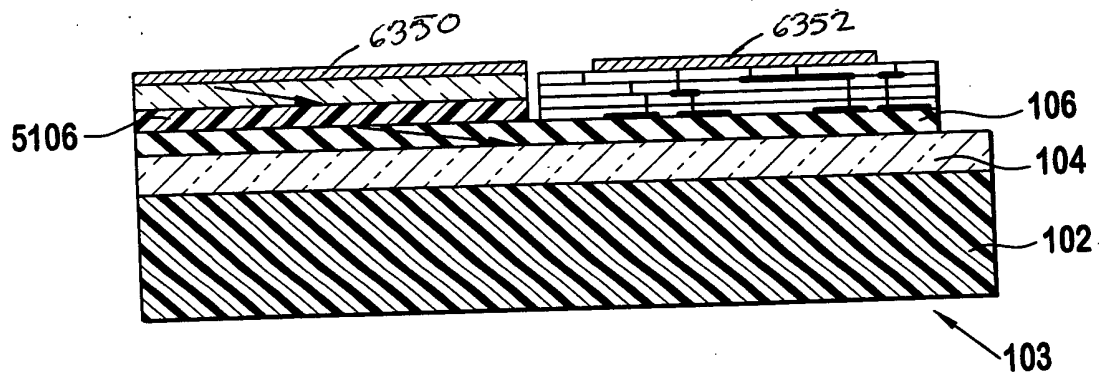


FIG. 63D



37/55

FIG. 64

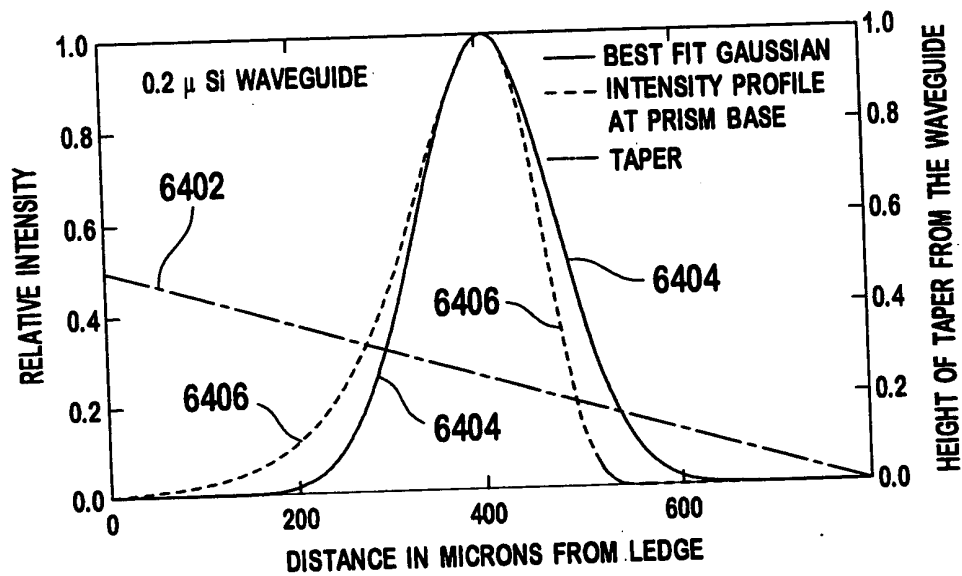
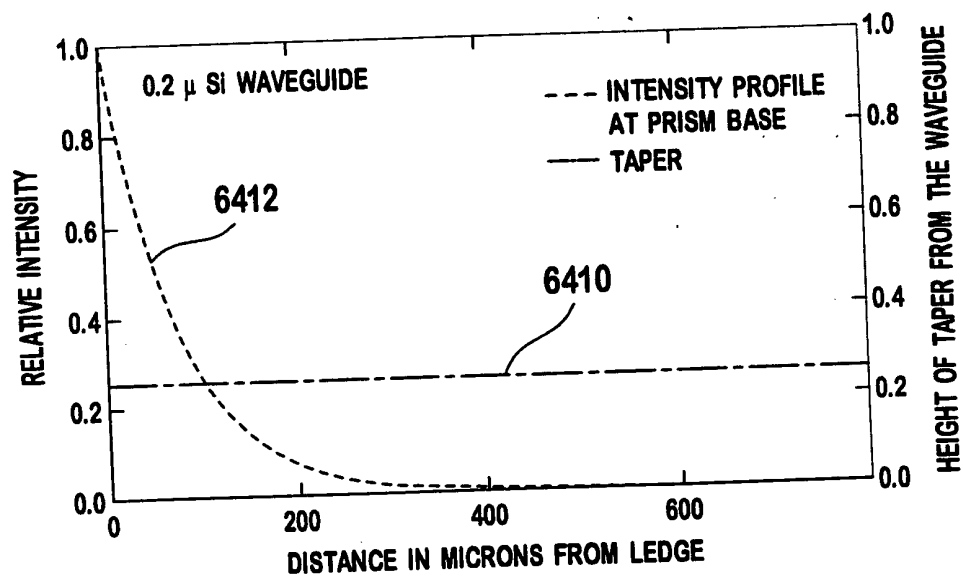


FIG. 65



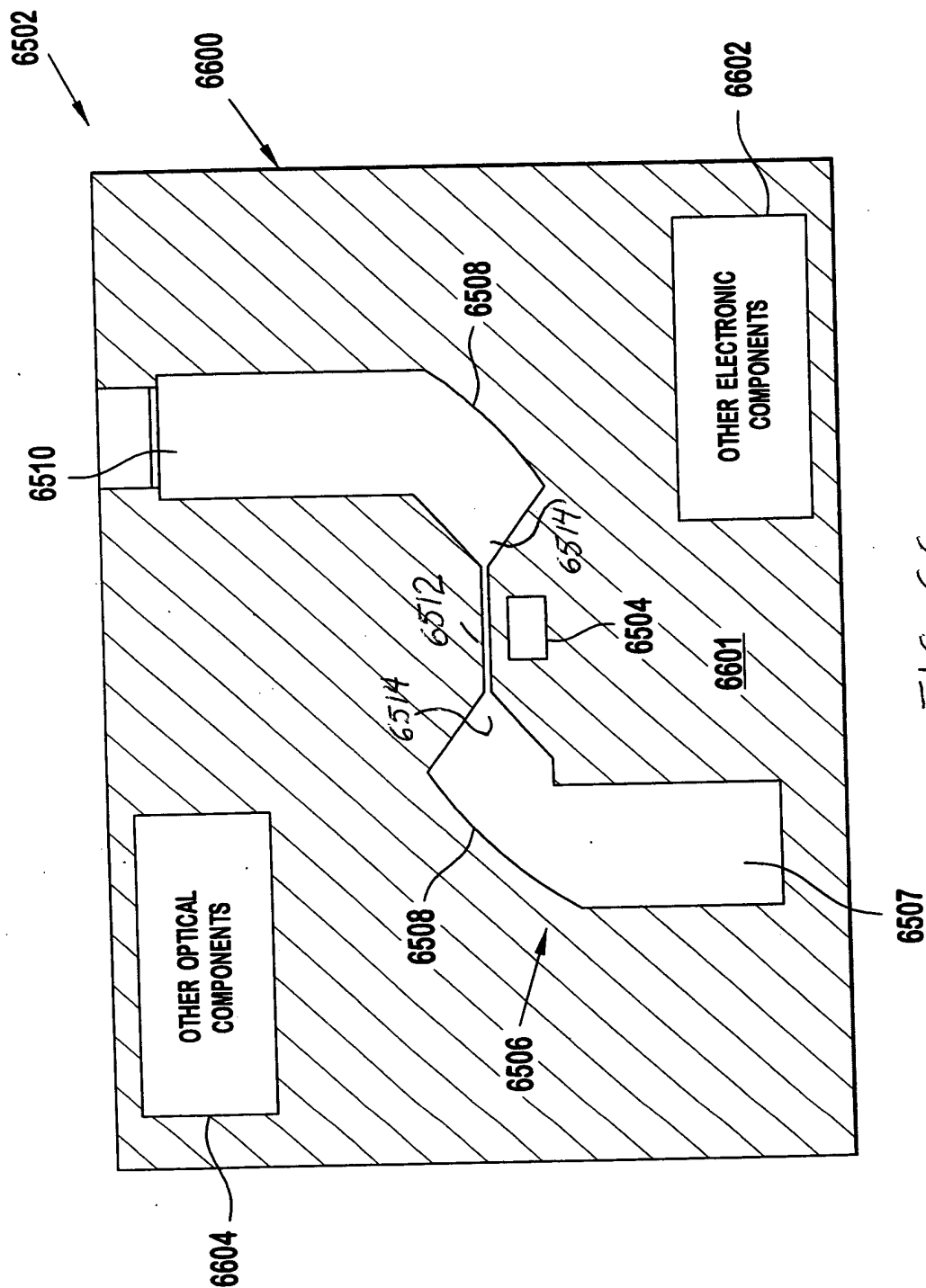


FIG. 66

39/55

FIG. 67

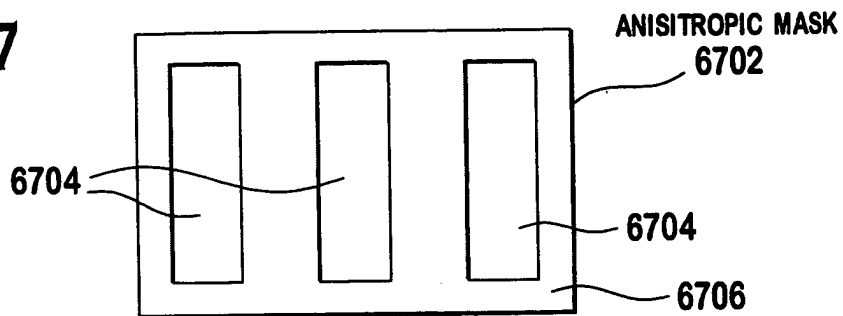


FIG. 68A



FIG. 68B

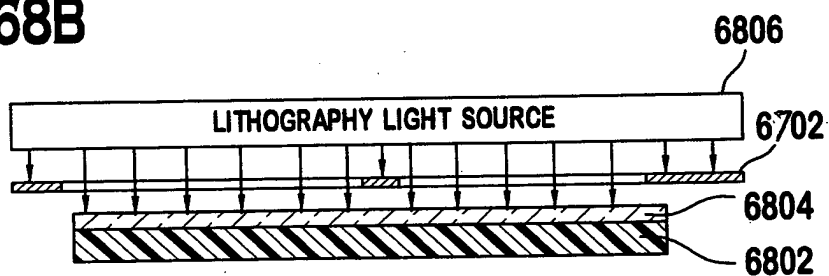
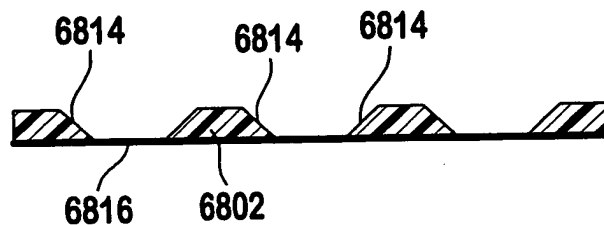


FIG. 68C



FIG. 68D



200220-89962001

40/55

FIG. 69

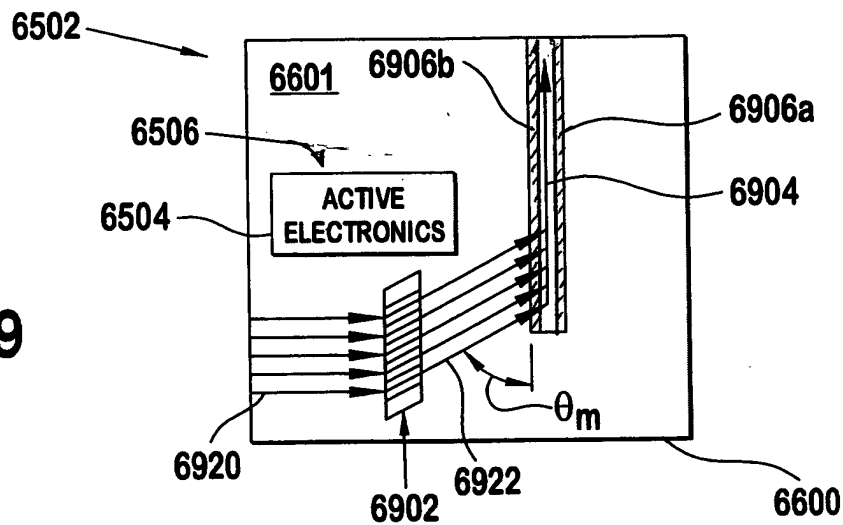


FIG. 70

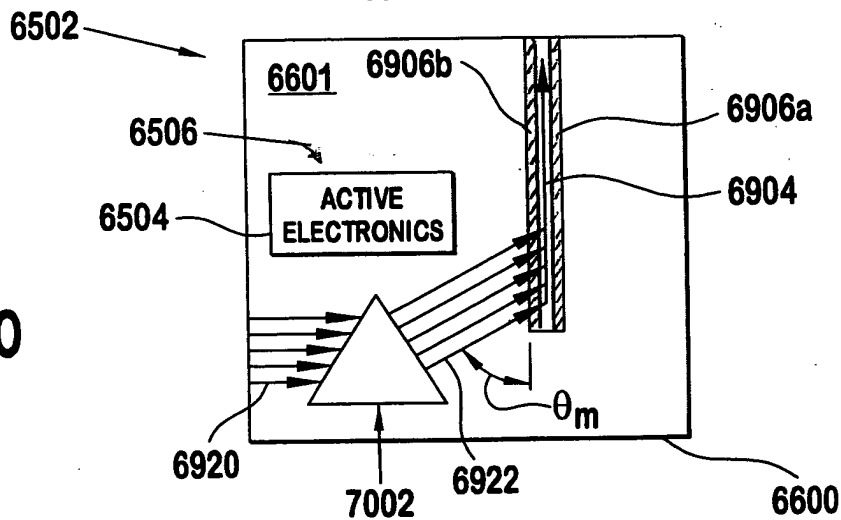
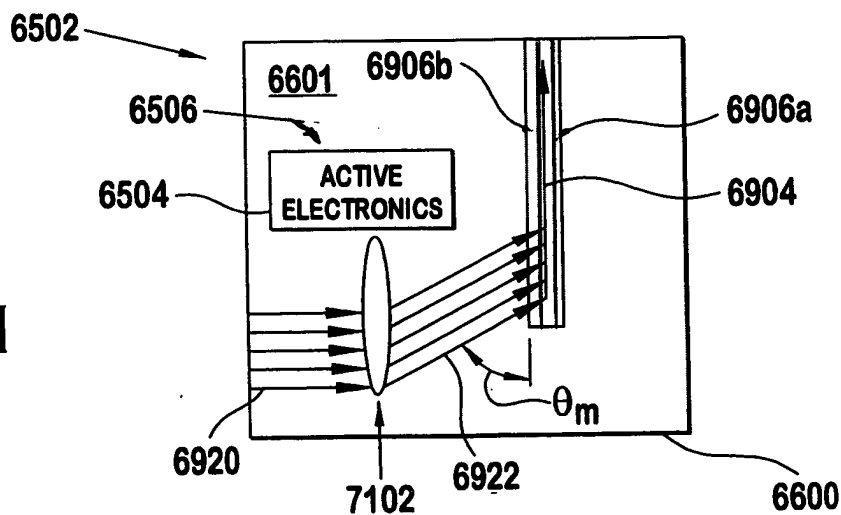


FIG. 71



200220-89962001

41/55

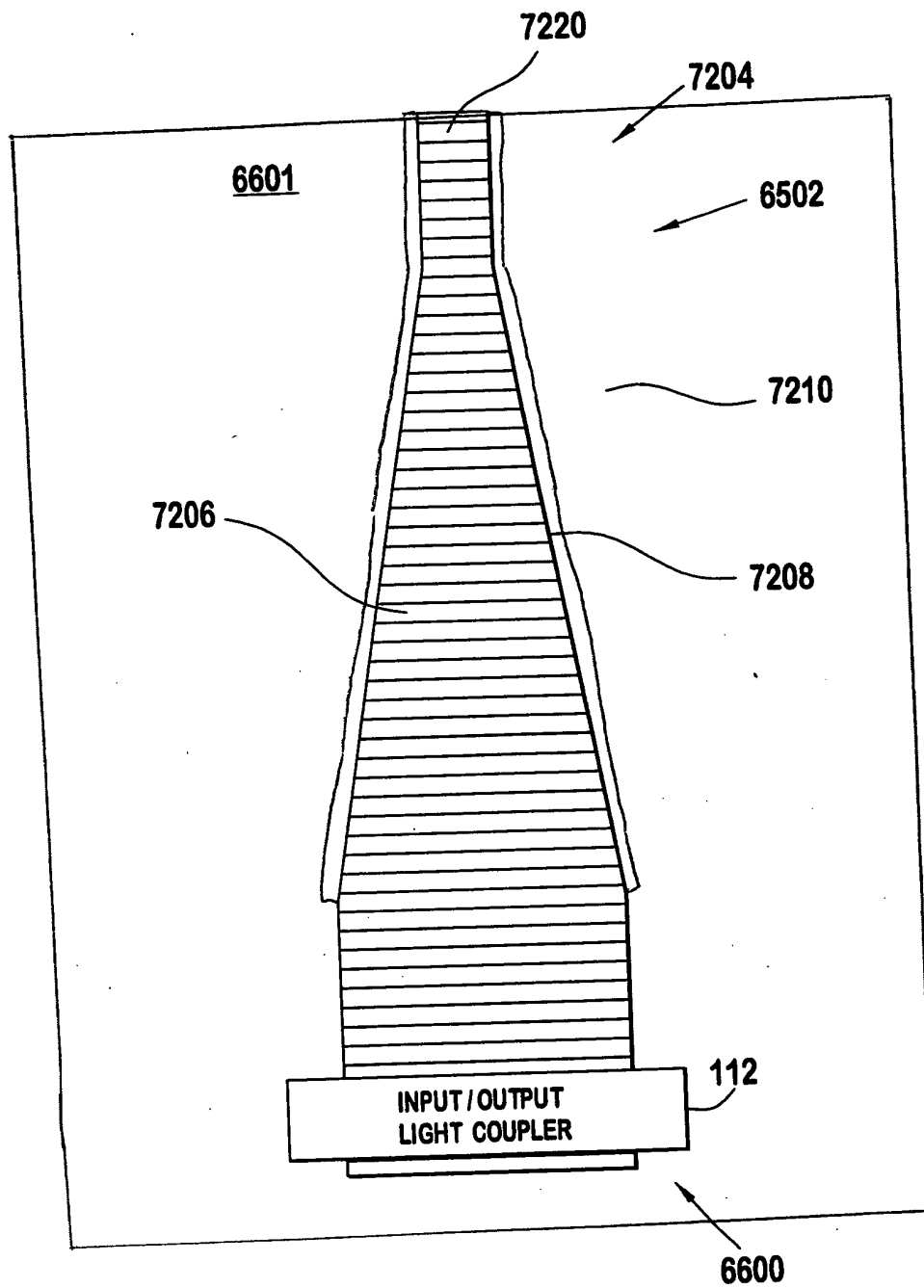


FIG. 72

200220-8996200T

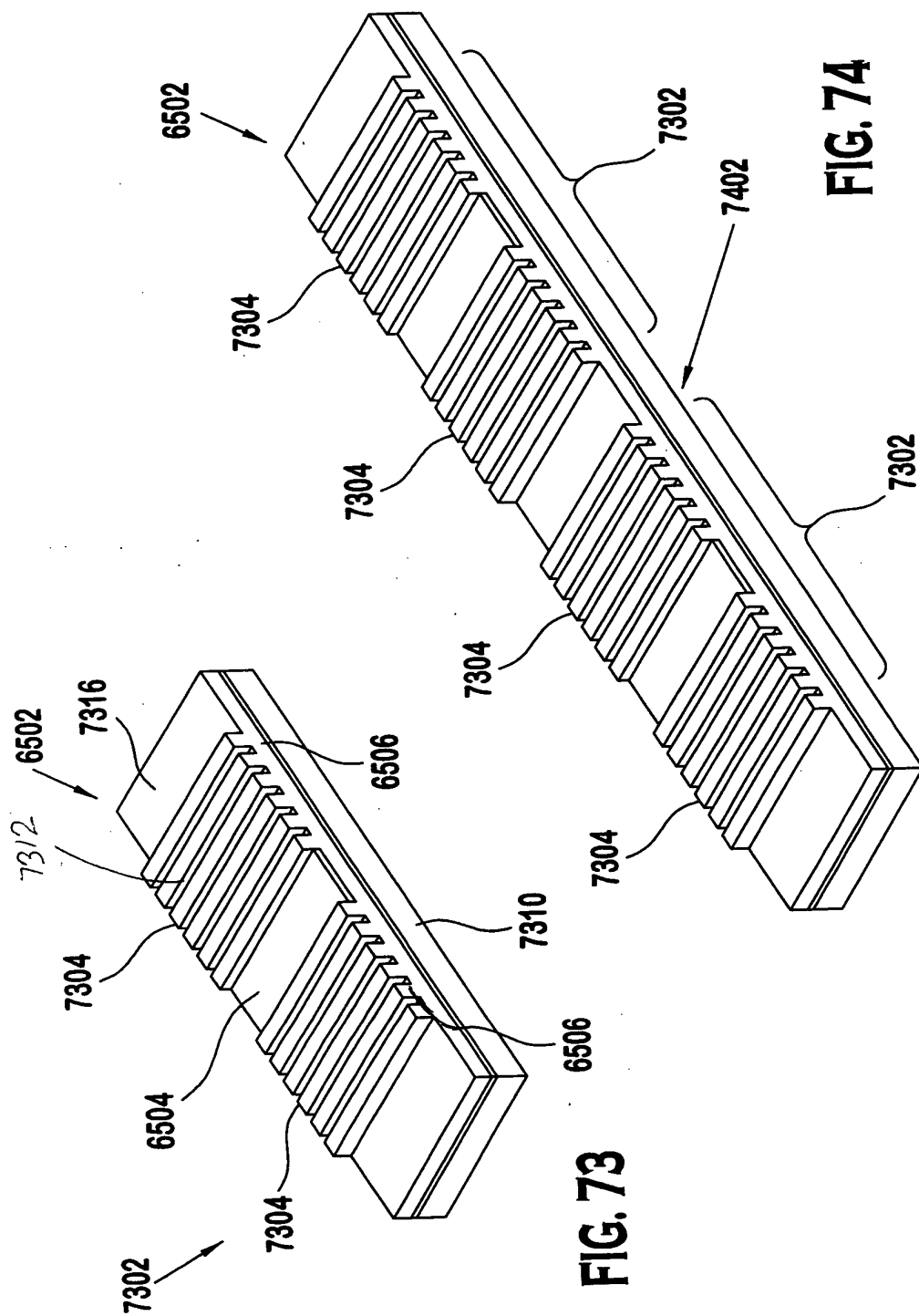


FIG. 73

FIG. 74

43/55

FIG. 75

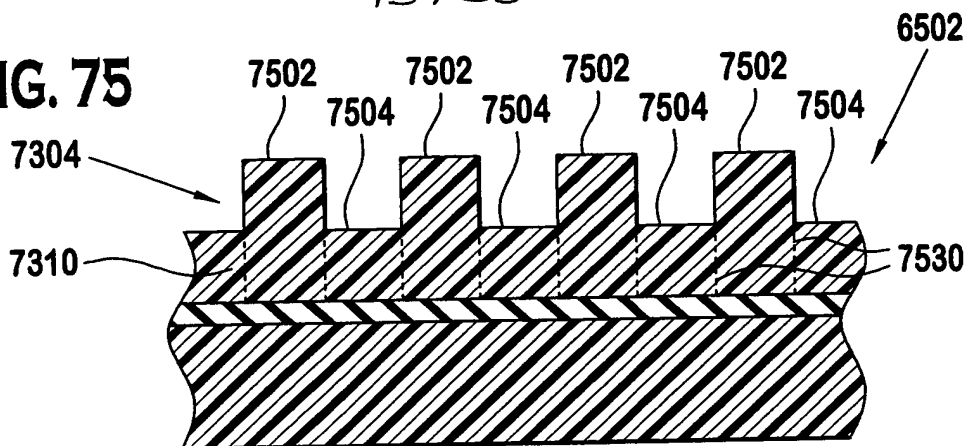


FIG. 76

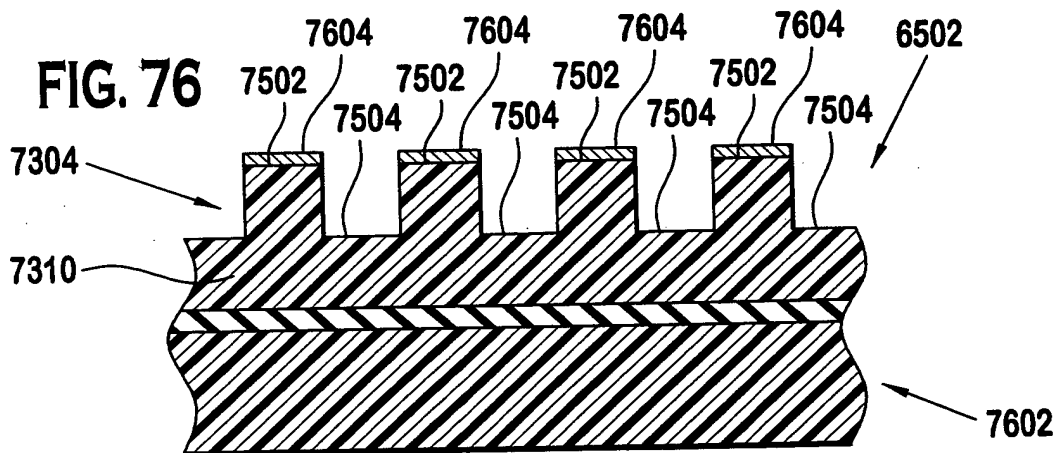
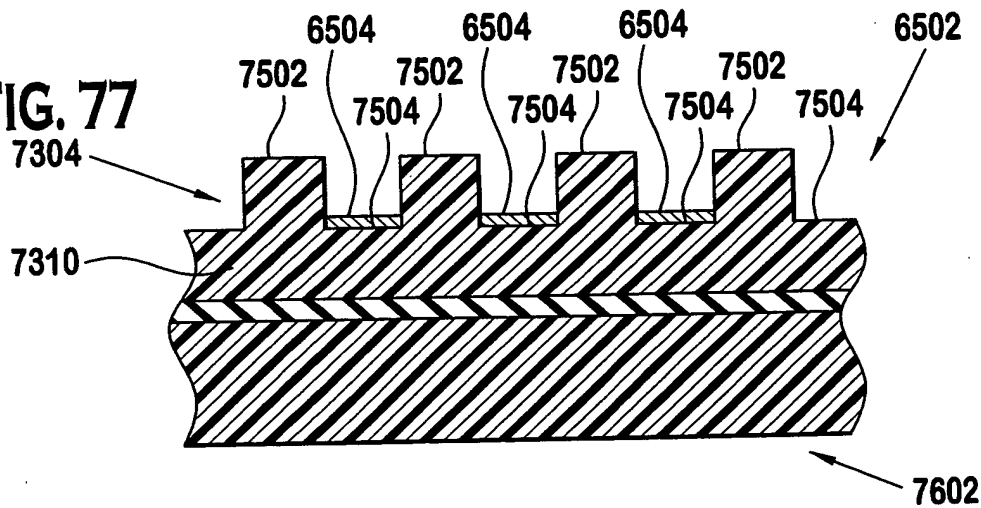


FIG. 77



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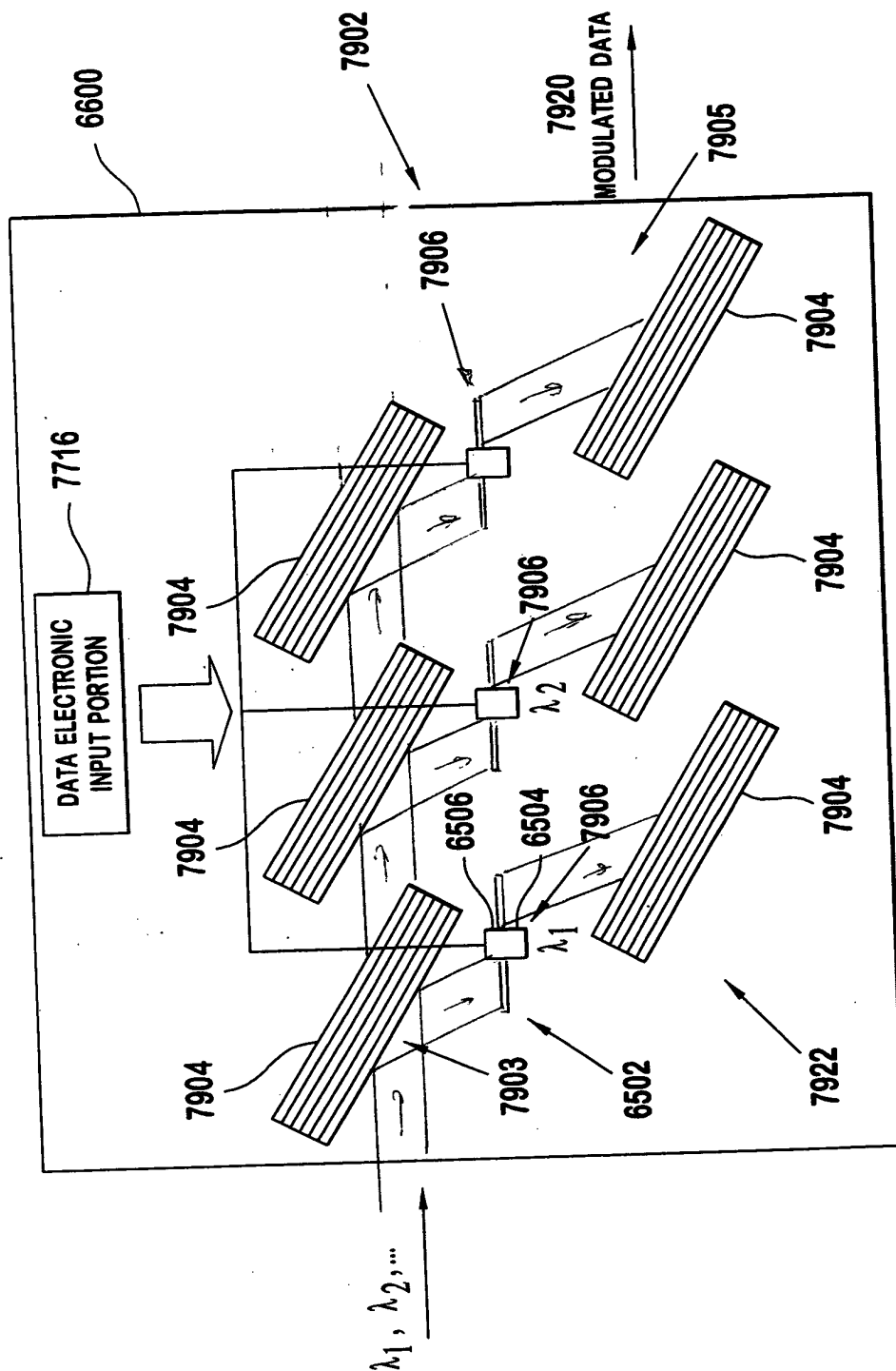


FIG. 79

46/55

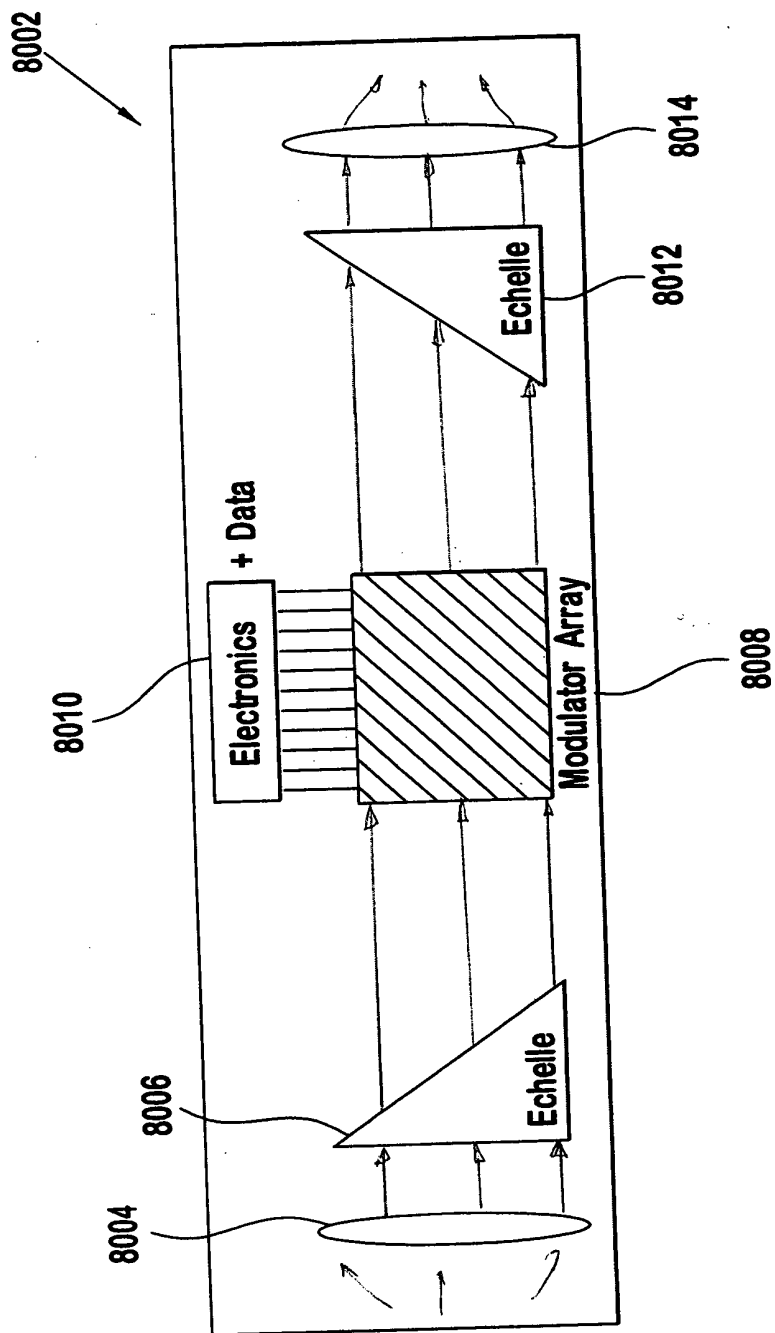


FIG. 80

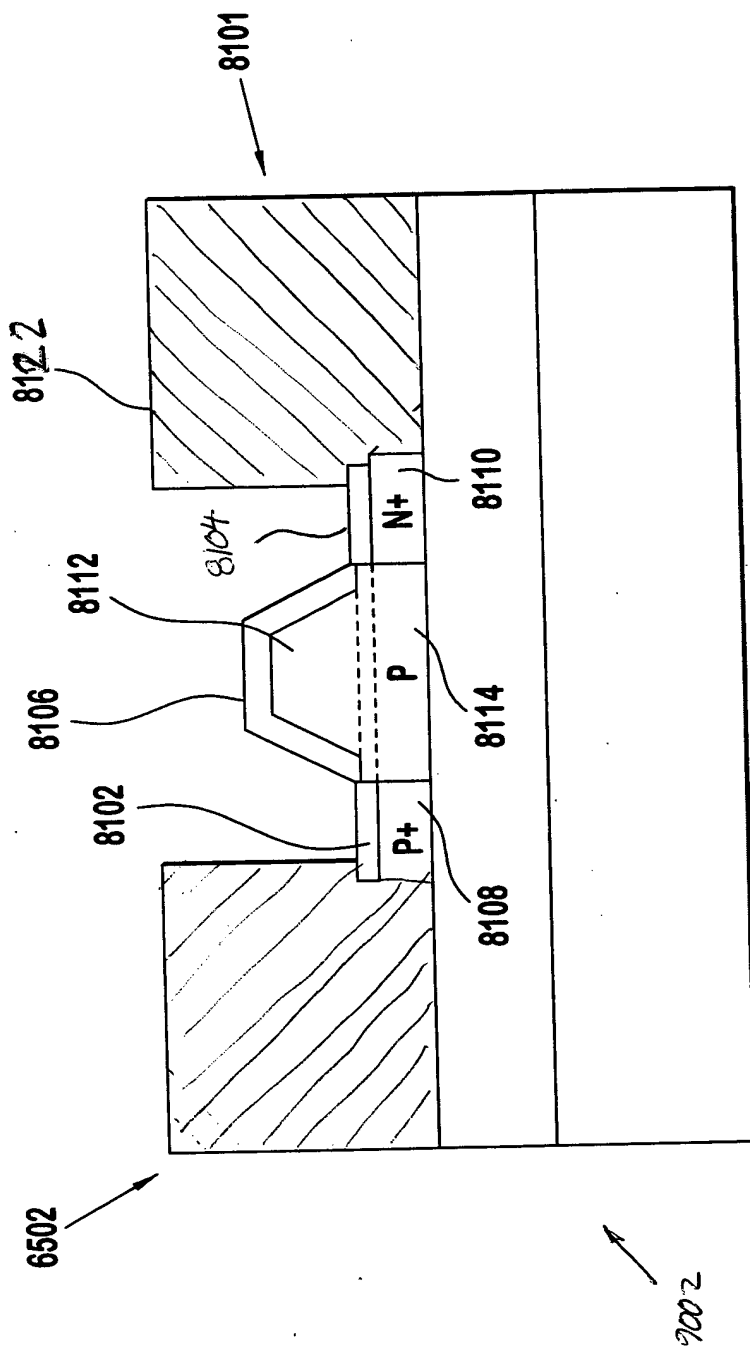


FIG. 81

FIG. 82

48/55.

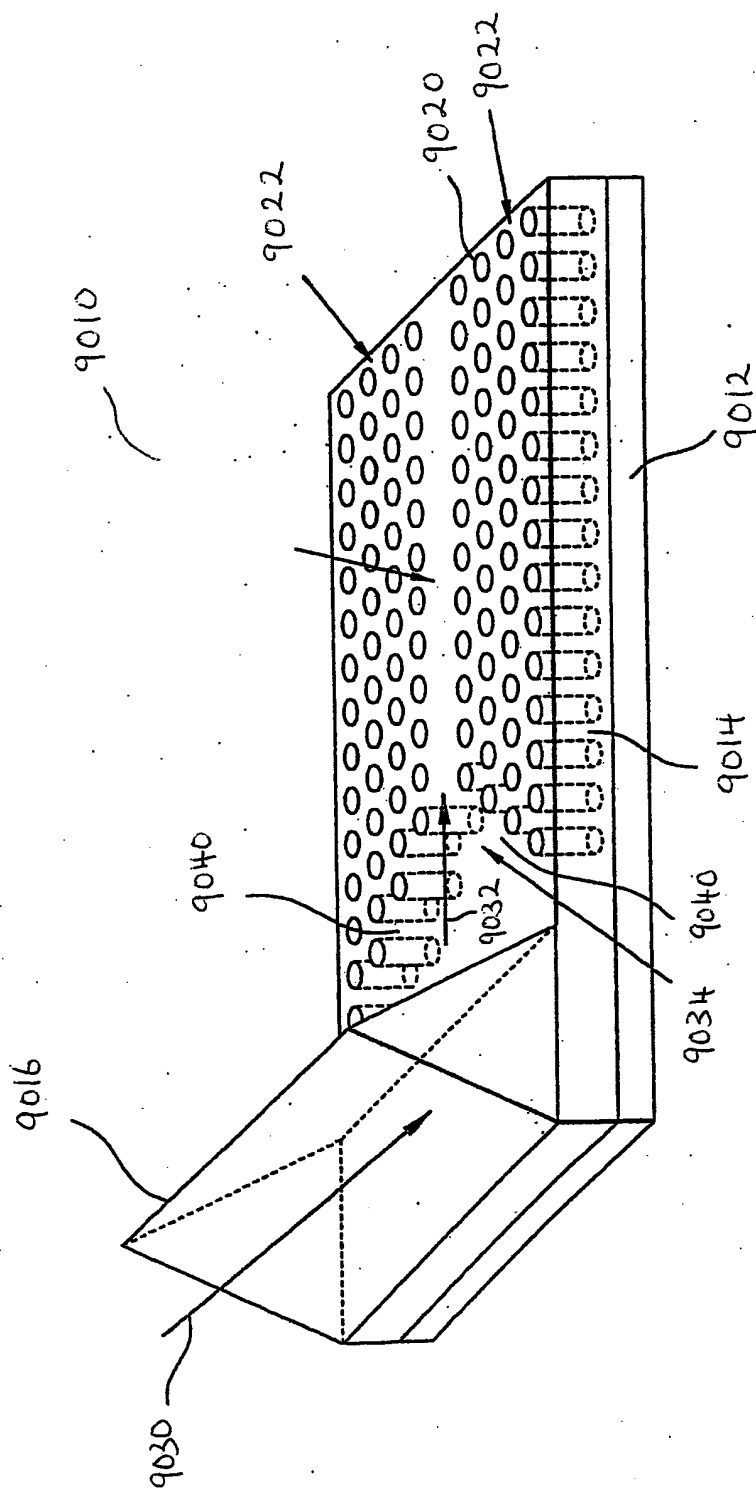
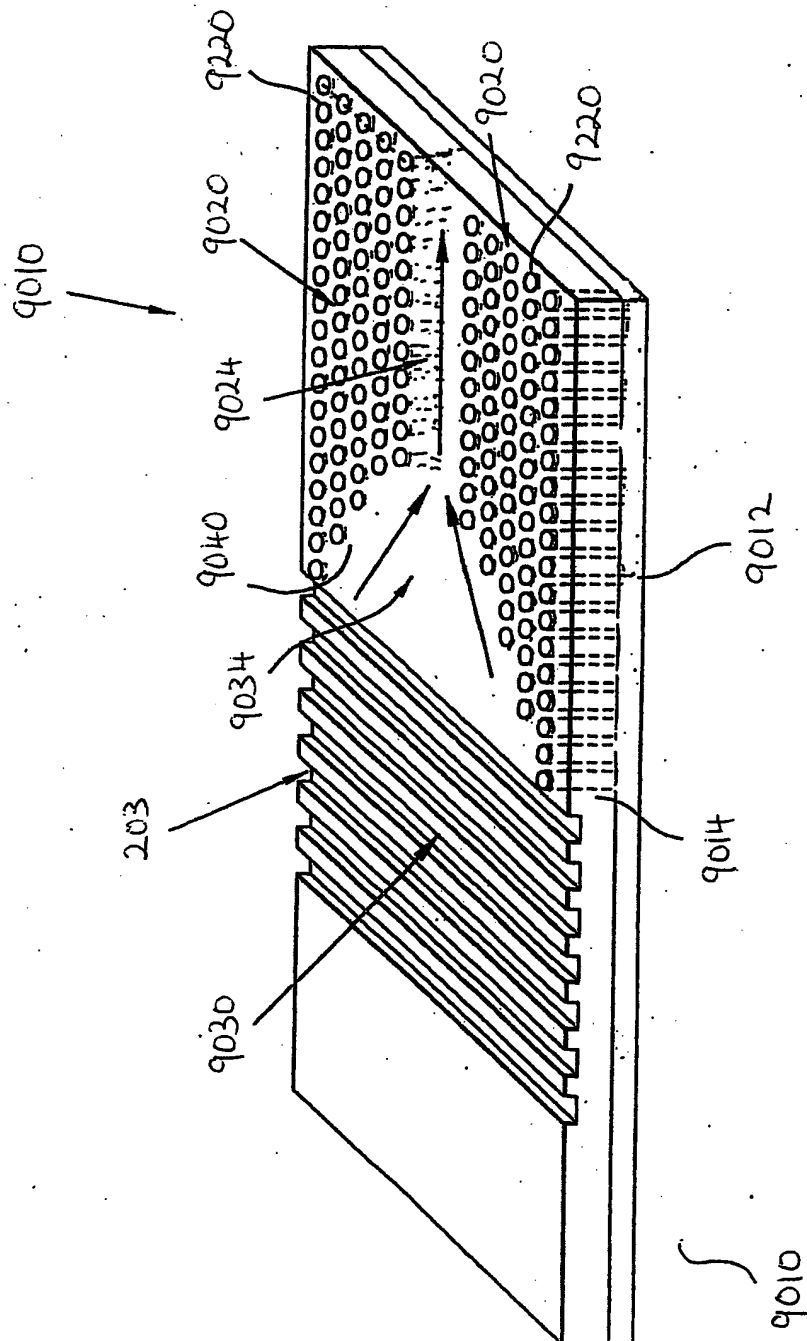


FIG. 83



50/55

FIG. 84

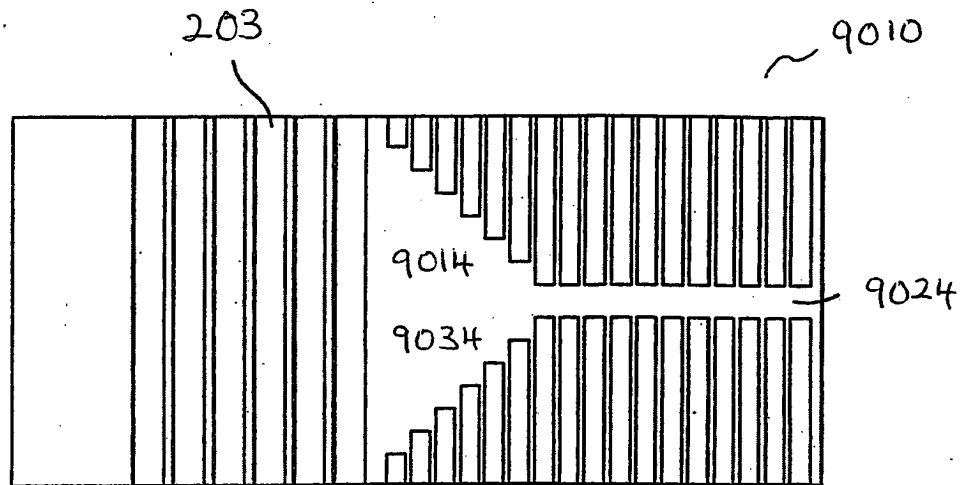
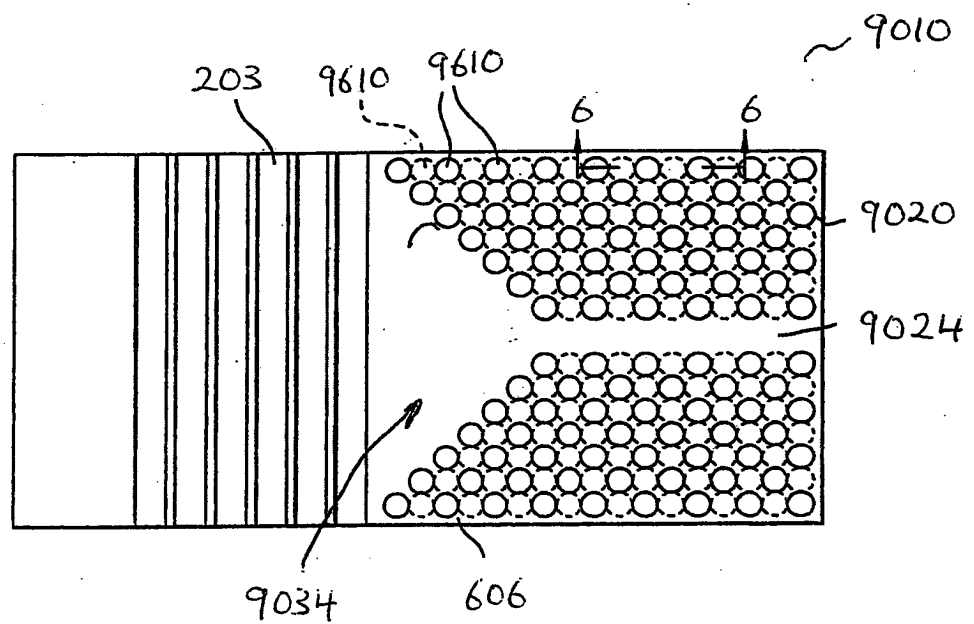


FIG. 85



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FIG. 86

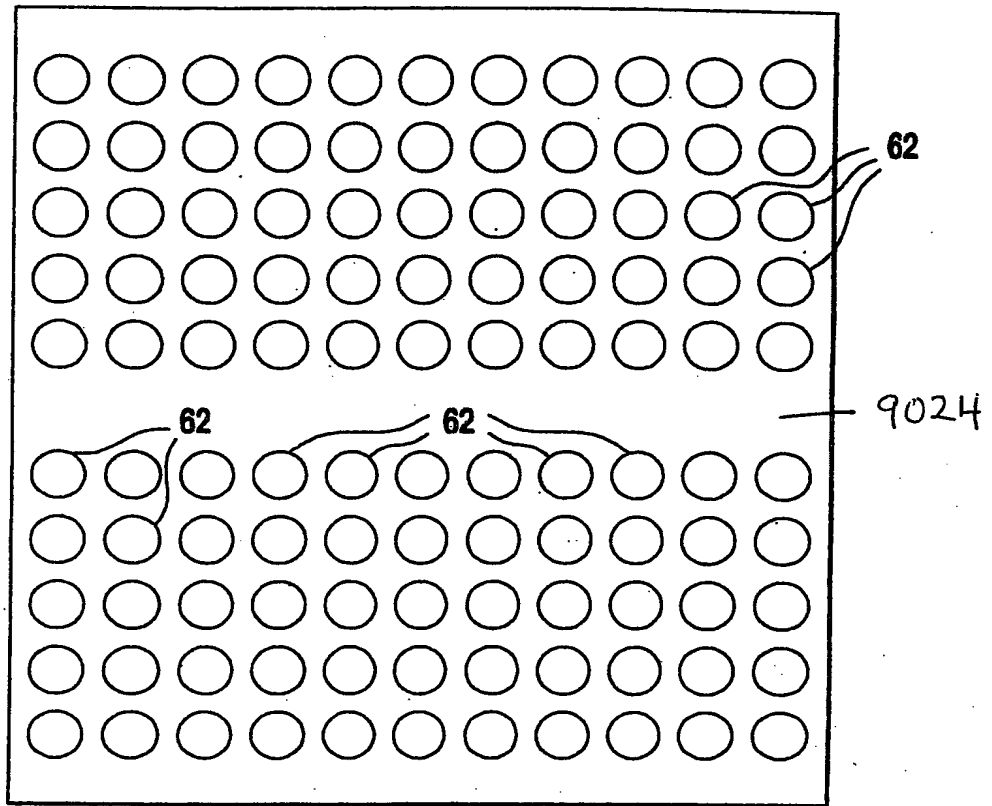


FIG. 87

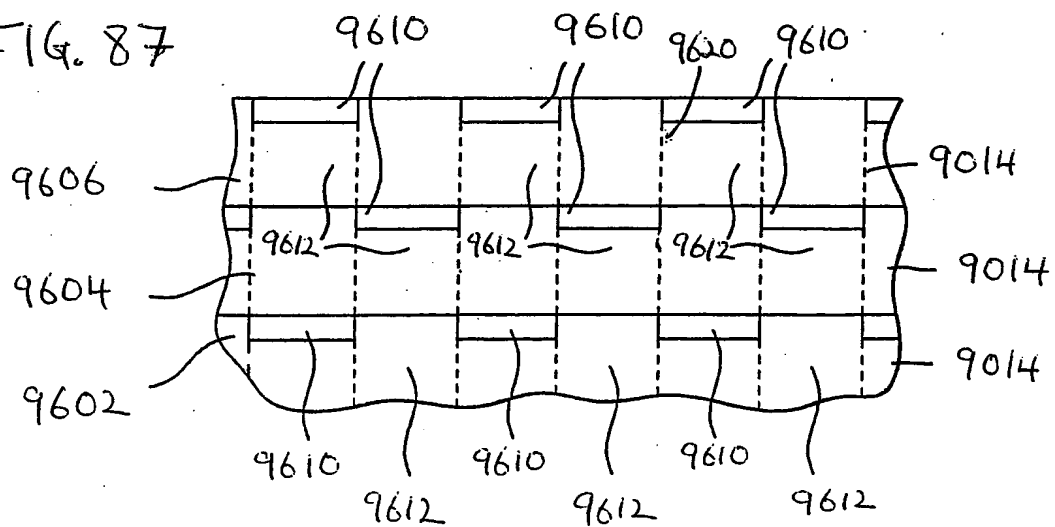
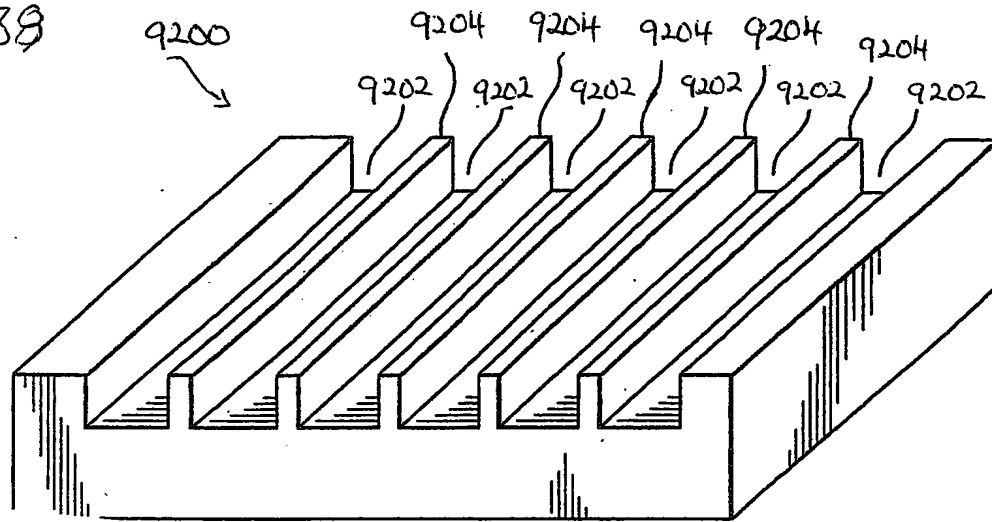


FIG. 88



10079668.022002

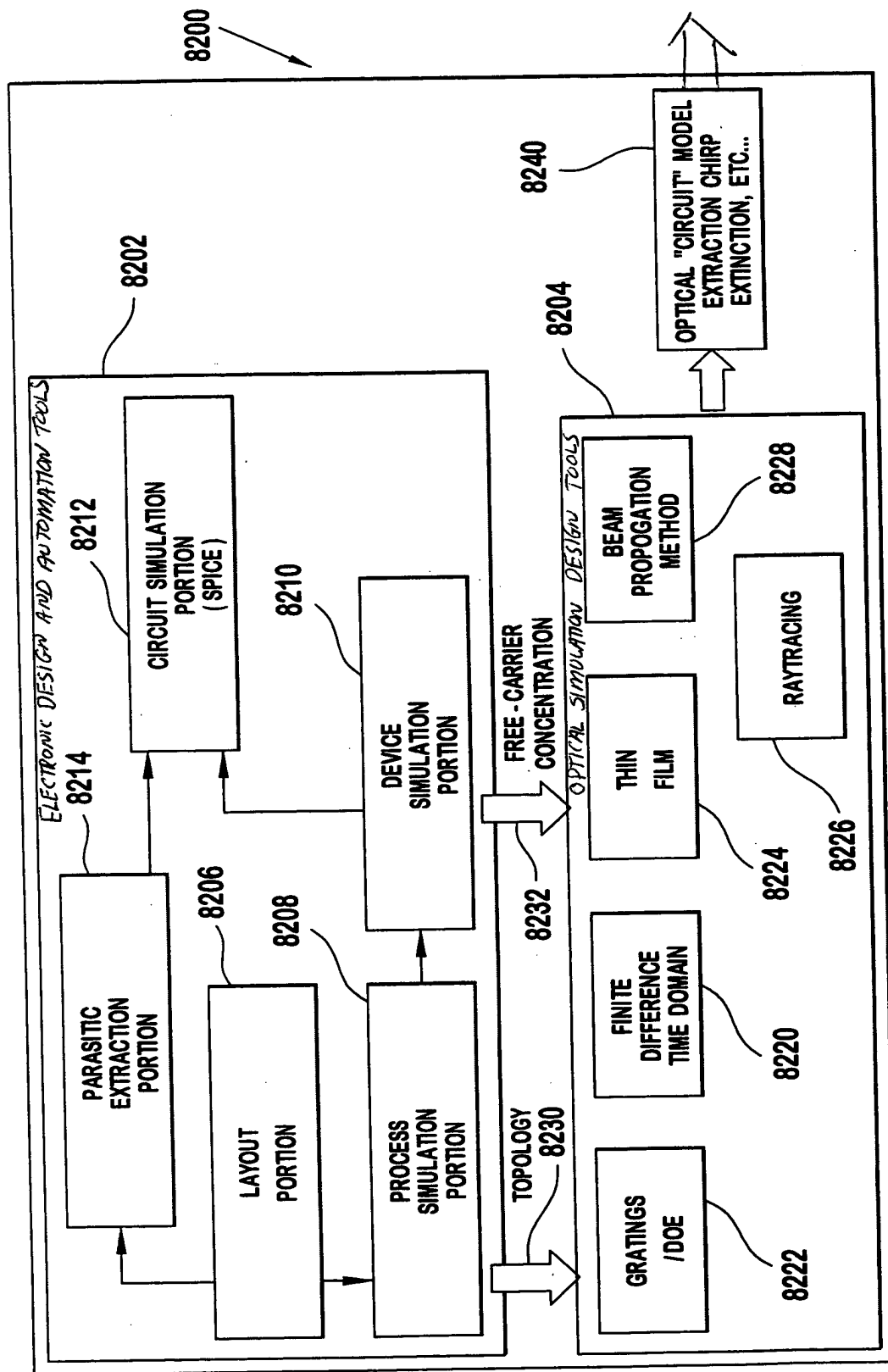


FIG. 8/9

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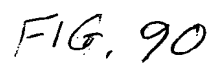


FIG. 90

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↓

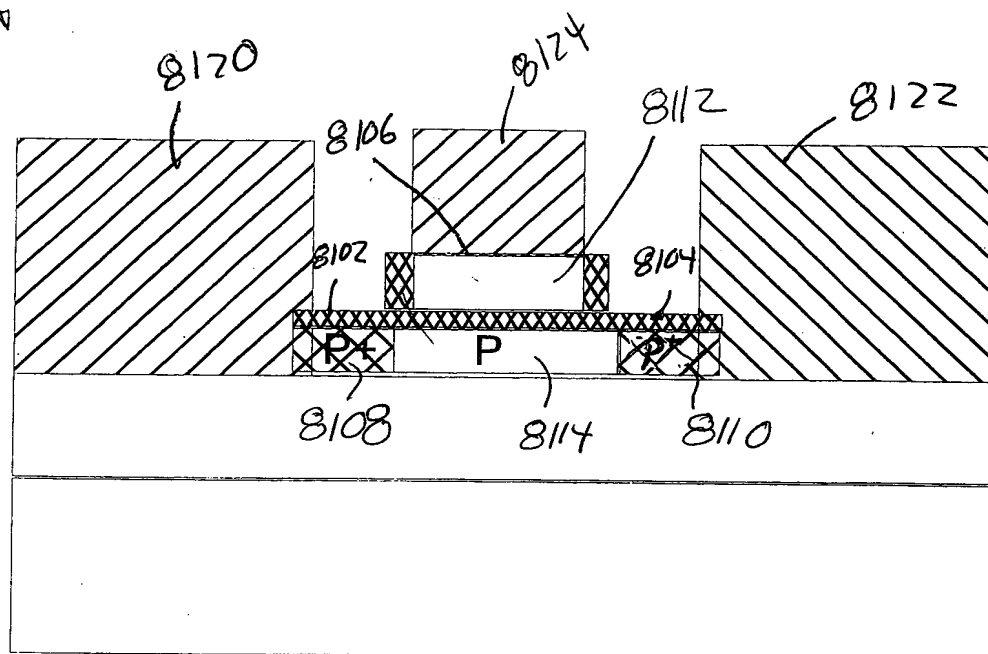


FIG. 91